



FEATURES

Rail-to-rail input/output
Low power: 0.625 mA typical per amplifier at ± 15 V
Gain bandwidth product: 15.9 MHz at $A_v = 100$ typical
Unity-gain crossover: 9.9 MHz typical
–3 dB closed-loop bandwidth: 13.9 MHz typical at ± 15 V
Low offset voltage: 100 μ V maximum (SOIC)
Unity-gain stable
High slew rate: 4.6 V/ μ s typical
Low noise: 3.9 nV/ $\sqrt{\text{Hz}}$ typical at 1 kHz

APPLICATIONS

Battery-powered instrumentation
High-side and low-side sensing
Power supply control and protection
Telecommunications
Digital-to-analog converter (DAC) output amplifiers
Analog-to-digital converter (ADC) input buffers

GENERAL DESCRIPTION

The [ADA4084-1](#) (single), [ADA4084-2](#) (dual), and [ADA4084-4](#) (quad) are single-supply, 10 MHz bandwidth amplifiers featuring rail-to-rail inputs and outputs. They are guaranteed to operate from +3 V to +30 V (or ± 1.5 V to ± 15 V).

These amplifiers are well suited for single-supply applications requiring both ac and precision dc performance. The combination of wide bandwidth, low noise, and precision makes the [ADA4084-1](#), [ADA4084-2](#), and [ADA4084-4](#) useful in a wide variety of applications, including filters and instrumentation.

Other applications for these amplifiers include portable telecommunications equipment, power supply control and protection, and use as amplifiers or buffers for transducers with wide output ranges. Sensors requiring a rail-to-rail input amplifier include Hall effect, piezoelectric, and resistive transducers.

The ability to swing rail to rail at both the input and output enables designers to build multistage filters in single-supply systems and to maintain high signal-to-noise ratios.

The [ADA4084-1](#), [ADA4084-2](#), and [ADA4084-4](#) are specified over the industrial temperature range of -40°C to $+125^{\circ}\text{C}$. The single [ADA4084-1](#) is available in the 8-lead SOIC; the dual [ADA4084-2](#) is available in the 8-lead SOIC, 8-lead MSOP, and 8-lead LFCSP surface-mount packages; and the [ADA4084-4](#) is offered in the 14-lead TSSOP and 16-lead LFCSP.

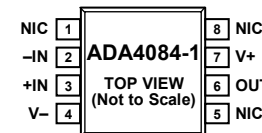
The [ADA4084-1](#), [ADA4084-2](#), and [ADA4084-4](#) are members of a growing series of high voltage, low noise op amps offered by Analog Devices, Inc. (see Table 1).

Rev. G

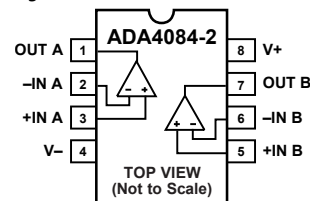
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PIN CONFIGURATIONS



NOTES
 1. NIC = NOT INTERNALLY CONNECTED.
 Figure 1. [ADA4084-1](#), 8-Lead SOIC (R)



NOTES
 1. FOR THE LFCSP PACKAGE, THE EXPOSED PAD MUST BE CONNECTED TO V-.

Figure 2. [ADA4084-2](#), 8-Lead MSOP (RM), 8-Lead SOIC (R), 8-Lead LFCSP (CP)

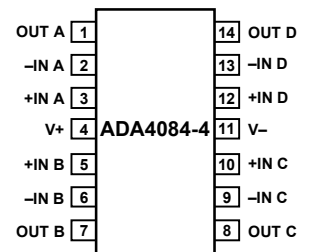
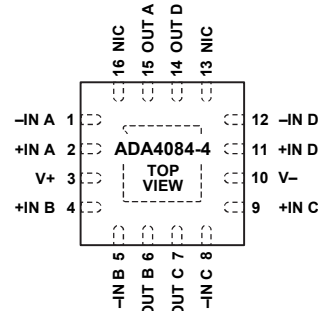


Figure 3. [ADA4084-4](#), 14-Lead TSSOP (RU)



NOTES
 1. NIC = NOT INTERNALLY CONNECTED.
 2. FOR THE LFCSP PACKAGE, THE EXPOSED PAD MUST BE CONNECTED TO V-.

Figure 4. [ADA4084-4](#), 16-Lead LFCSP (CP)

Table 1. Low Noise Op Amps

Single	Dual	Quad	Voltage Noise
AD8597	AD8599		1.1 nV/Hz
ADA4004-1	ADA4004-2	ADA4004-4	1.8 nV/Hz
AD8675	AD8676		2.8 nV/Hz rail-to-rail output
AD8671	AD8672	AD8674	2.8 nV/Hz
OP27, OP37			3.2 nV/Hz
ADA4084-1	ADA4084-2	ADA4084-4	3.9 nV/Hz rail-to-rail input/output

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Changes to Figure 96 and Figure 9724

1/15—Rev. E to Rev. F

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7/14—Rev. D to Rev. E

Added ADA4804-1 Universal

Added Figure 1; Renumbered Sequentially 1

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Changes to Current Noise Density Parameter, Table 34

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11/13—Rev. C to Rev. D

Added 14-Lead TSSOP and 16-Lead LFCSP Packages..... Universal

Added ADA4804-4..... Universal

Change to Features Section and Applications Section 1

Added Figure 2 and Figure 3; Renumbered Sequentially 1

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Updated Outline Dimensions.....27

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4/13—Rev. B to Rev. C

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6/12—Rev. A to Rev. B

Added LFCSP Package Universal

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10/11—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS

$V_{SY} = 3\text{ V}$, $V_{CM} = 1.5\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V _{OS}	SOIC package		20	100	μV
		−40°C ≤ T _A ≤ +125°C			200	μV
		MSOP, TSSOP packages		50	130	μV
		−40°C ≤ T _A ≤ +125°C			250	μV
		ADA4084-2 LFCSP package		80	200	μV
		−40°C ≤ T _A ≤ +125°C			300	μV
Offset Voltage Drift	ΔV _{OS} /ΔT	−40°C ≤ T _A ≤ +125°C		0.5	1.75	μV/°C
Offset Voltage Matching		T _A = 25°C			150	μV
ADA4084-4 LFCSP package				200	μV	
Input Bias Current	I _B			140	250	nA
Input Offset Current	I _{OS}	−40°C ≤ T _A ≤ +125°C			400	nA
				5	25	nA
		−40°C ≤ T _A ≤ +125°C			50	nA
Input Voltage Range	CMRR		0		3	V
Common-Mode Rejection Ratio		64	88		dB	
		60			dB	
Large Signal Voltage Gain	A _{VO}	R _L = 2 kΩ, 0.5 V ≤ V _{OUT} ≤ 2.5 V	100	104		dB
		R _L = 2 kΩ, −40°C ≤ T _A ≤ +125°C	97			dB
Input Impedance						
Differential				100 1.1		kΩ pF
Common Mode				80 2.9		MΩ pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	R _L = 10 kΩ to V _{CM}	2.90	2.95		V
		−40°C ≤ T _A ≤ +125°C	2.80			V
		R _L = 2 kΩ to V _{CM}	2.85	2.9		V
		−40°C ≤ T _A ≤ +125°C	2.70			V
Output Voltage Low	V _{OL}	R _L = 10 kΩ to V _{CM}		10	20	mV
		−40°C ≤ T _A ≤ +125°C			40	mV
		R _L = 2 kΩ to V _{CM}		20	30	mV
		−40°C ≤ T _A ≤ +125°C			50	mV
Short-Circuit Current	I _{SC}			−17/+10		mA
Closed-Loop Output Impedance	Z _{OUT}	f = 1 kHz, A _V = 1		0.1		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V _{SY} = ±1.25 V to ±1.75 V	100	110		dB
		−40°C ≤ T _A ≤ +125°C	90			dB
Supply Current per Amplifier	I _{SY}	I _{OUT} = 0 mA		0.565	0.650	mA
		−40°C ≤ T _A ≤ +125°C			0.950	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R _L = 2 kΩ	2.0	2.6		V/μs
Gain Bandwidth Product	GBP	V _{IN} = 5 mV p-p, R _L = 10 kΩ, A _V = 100		15.4		MHz
Unity-Gain Crossover	UGC	V _{IN} = 5 mV p-p, R _L = 10 kΩ, A _V = 1		8.08		MHz
Phase Margin	Φ _M			86		Degrees
−3 dB Closed-Loop Bandwidth	−3 dB	A _V = 1, V _{IN} = 5 mV p-p		12.3		MHz
Settling Time	t _s	A _V = 10, V _{IN} = 2 V p-p, 0.1%		4		μs
Total Harmonic Distortion Plus Noise	THD + N	V _{IN} = 300 mV rms, R _L = 2 kΩ, f = 1 kHz		0.009		%
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	0.1 Hz to 10 Hz		0.14		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		3.9		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		0.55		pA/√Hz

$V_{SY} = \pm 5.0\text{ V}$, $V_{CM} = 0\text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 3.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V _{OS}	SOIC package		30	100	μV
		−40°C ≤ T _A ≤ +125°C			200	μV
		MSOP, TSSOP packages		60	130	μV
		−40°C ≤ T _A ≤ +125°C			250	μV
		ADA4084-2 LFCSP package		90	200	μV
		−40°C ≤ T _A ≤ +125°C			300	μV
Offset Voltage Drift	ΔV _{OS} /ΔT	−40°C ≤ T _A ≤ +125°C	0.5	1.75	μV/°C	
Offset Voltage Matching		T _A = 25°C		150	μV	
ADA4084-4 LFCSP package			200	μV		
Input Bias Current	I _B		140	250	nA	
Input Offset Current	I _{OS}	−40°C ≤ T _A ≤ +125°C			400	nA
			5	25	nA	
		−40°C ≤ T _A ≤ +125°C			50	nA
Input Voltage Range	CMRR		−5		+5	V
Common-Mode Rejection Ratio		V _{CM} = ±4 V, −40°C ≤ T _A ≤ +125°C	106	124		dB
		V _{CM} = ±5 V	76			dB
		V _{CM} = ±5 V, −40°C ≤ T _A ≤ +125°C	70			dB
Large Signal Voltage Gain	A _{VO}	R _L = 2 kΩ, −4 V ≤ V _{OUT} ≤ 4 V	108	112		dB
		R _L = 2 kΩ, −40°C ≤ T _A ≤ +125°C	103			dB
Input Impedance				100 1.1		kΩ pF
Differential				200 2.5		MΩ pF
Common Mode						
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	R _L = 10 kΩ to V _{CM}	4.9	4.95		V
		−40°C ≤ T _A ≤ +125°C	4.8			V
		R _L = 2 kΩ to V _{CM}	4.8	4.85		V
		−40°C ≤ T _A ≤ +125°C	4.7			V
Output Voltage Low	V _{OL}	R _L = 10 kΩ to V _{CM}		−4.95	−4.9	V
		−40°C ≤ T _A ≤ +125°C			−4.8	V
		R _L = 2 kΩ to V _{CM}		−4.95	−4.8	V
		−40°C ≤ T _A ≤ +125°C			−4.7	V
Short-Circuit Current	I _{SC}			−24/+17		mA
Closed-Loop Output Impedance	Z _{OUT}	f = 1 kHz, A _V = 1		0.1		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V _{SY} = ±2 V to ±18 V	110	120		dB
		−40°C ≤ T _A ≤ +125°C	105			dB
Supply Current per Amplifier	I _{SY}	I _{OUT} = 0 mA		0.595	0.700	mA
		−40°C ≤ T _A ≤ +125°C			1.00	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R _L = 2 kΩ to V _{CM}	2.4	3.7		V/μs
Gain Bandwidth Product	GBP	V _{IN} = 5 mV p-p, R _L = 10 kΩ, A _V = 100		15.9		MHz
Unity-Gain Crossover	UGC	V _{IN} = 5 mV p-p, R _L = 10 kΩ, A _V = 1		9.6		MHz
Phase Margin	Φ _M			85		Degrees
−3 dB Closed-Loop Bandwidth	−3 dB	A _V = 1, V _{IN} = 5 mV p-p		13.9		MHz
Settling Time	t _s	A _V = 10, V _{IN} = 8 V p-p, 0.1%		4		μs
Total Harmonic Distortion Plus Noise	THD + N	V _{IN} = 2 V rms, R _L = 2 kΩ, f = 1 kHz		0.003		%
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	0.1 Hz to 10 Hz		0.14		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		3.9		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		0.55		pA/√Hz

$V_{SY} = \pm 15.0 \text{ V}$, $V_{CM} = 0 \text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V _{OS}	SOIC package −40°C ≤ T _A ≤ +125°C MSOP, TSSOP packages −40°C ≤ T _A ≤ +125°C ADA4084-2 LFCSP package −40°C ≤ T _A ≤ +125°C		40 70 100	100 200 200 300	μV μV μV μV μV
Offset Voltage Drift	ΔV _{OS} /ΔT			0.5	1.75	μV/°C
Offset Voltage Matching		T _A = 25°C ADA4084-4 LFCSP package			150 200	μV μV
Input Bias Current	I _B	−40°C ≤ T _A ≤ +125°C		140	250	nA
Input Offset Current	I _{OS}	−40°C ≤ T _A ≤ +125°C		5	25 50	nA nA
Input Voltage Range			−15		+15	V
Common-Mode Rejection Ratio	CMRR	V _{CM} = ±14 V, −40°C ≤ T _A ≤ +125°C V _{CM} = ±15 V V _{CM} = ±15 V, −40°C ≤ T _A ≤ +125°C	106 85 80	124		dB dB dB
Large Signal Voltage Gain	A _{VO}	R _L = 2 kΩ, −13.5 V ≤ V _{OUT} ≤ +13.5 V −40°C ≤ T _A ≤ +125°C	110 105	117		dB dB
Input Impedance						
Differential				100 1.1		kΩ pF
Common Mode				200 2.5		MΩ pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	R _L = 10 kΩ to V _{CM} −40°C ≤ T _A ≤ +125°C R _L = 2 kΩ to V _{CM} −40°C ≤ T _A ≤ +125°C	14.85 14.8 14.5 14.0	14.9		V V V V
Output Voltage Low	V _{OL}	R _L = 10 kΩ to V _{CM} −40°C ≤ T _A ≤ +125°C R _L = 2 kΩ to V _{CM} −40°C ≤ T _A ≤ +125°C		−14.95 −14.9	−14.9 −14.8 −14.7	V V V V
Short-Circuit Current	I _{SC}			±30		mA
Closed-Loop Output Impedance	Z _{OUT}	f = 1 kHz, A _V = +1		0.1		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V _{SY} = ±2 V to ±18 V −40°C ≤ T _A ≤ +125°C	110 105	120		dB dB
Supply Current per Amplifier	I _{SY}	I _{OUT} = 0 mA −40°C ≤ T _A ≤ +125°C		0.625	0.750 1.050	mA mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R _L = 2 kΩ	2.4	4.6		V/μs
Gain Bandwidth Product	GBP	V _{IN} = 5 mV p-p, R _L = 10 kΩ, A _V = 100		15.9		MHz
Unity-Gain Crossover	UGC	V _{IN} = 5 mV p-p, R _L = 10 kΩ, A _V = 1		9.9		MHz
Phase Margin	Φ _M			86		Degrees
−3 dB Closed-Loop Bandwidth	−3 dB	A _V = 1, V _{IN} = 5 mV p-p		13.9		MHz
Settling Time	t _s	A _V = 10, V _{IN} = 10 V p-p, 0.1%		4		μs
Total Harmonic Distortion Plus Noise	THD + N	V _{IN} = 5 V rms, R _L = 2 kΩ, f = 1 kHz		0.003		%
NOISE PERFORMANCE						
Voltage Noise	e _n p-p	0.1 Hz to 10 Hz		0.1		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		3.9		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		0.55		pA/√Hz

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter	Rating
Supply Voltage	$\pm 18\text{ V}$
Input Voltage	$V_- \leq V_{IN} \leq V_+$
Differential Input Voltage ¹	$\pm 0.6\text{ V}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-40°C to $+125^\circ\text{C}$
Junction Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (Soldering 60 sec)	300°C
ESD	
Human Body Model ²	4.5 kV
Machine Model ³	200 V
Field-Induced Charged-Device Model (FICDM) ⁴	1.25 kV

¹ For input differential voltages greater than 0.6 V, limit the input current to less than 5 mA to prevent degradation or destruction of the input devices.

² Applicable standard: MIL-STD-883, Method 3015.7.

³ Applicable standard: JESD22-A115-A (ESD machine model standard of JEDEC).

⁴ Applicable standard: JESD22-C101-C (ESD FICDM standard of JEDEC).

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the device soldered on a 4-layer JEDEC standard printed circuit board (PCB) with zero airflow.

Table 6. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead SOIC-N (R-8)	121	43	$^\circ\text{C/W}$
8-Lead MSOP (RM-8)	142	45	$^\circ\text{C/W}$
8-Lead LFCSP (CP-8-12) ^{1,3}	84	40	$^\circ\text{C/W}$
14-Lead TSSOP (RU-14)	112	43	$^\circ\text{C/W}$
16-Lead LFCSP (CP-16-26) ^{2,3}	55	30	$^\circ\text{C/W}$

¹ Values are based on 4-layer (252P) JEDEC standard PCB, with four thermal vias. Exposed pad soldered to PCB.

² Values are based on 4-layer (252P) JEDEC standard PCB, with nine thermal vias. Exposed pad soldered to PCB.

³ θ_{JC} measured on top of package.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

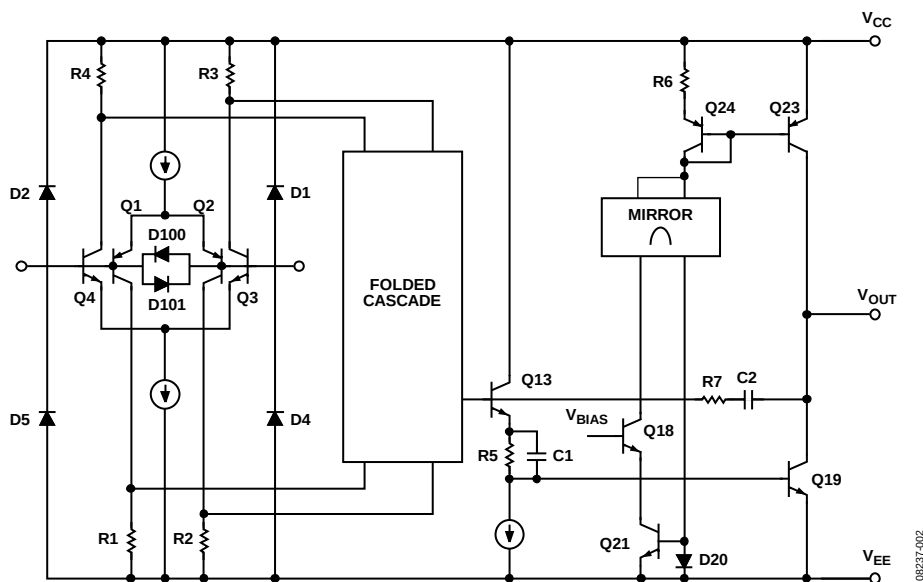


Figure 5. Simplified Schematic

TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

$\pm 1.5\text{ V}$ CHARACTERISTICS

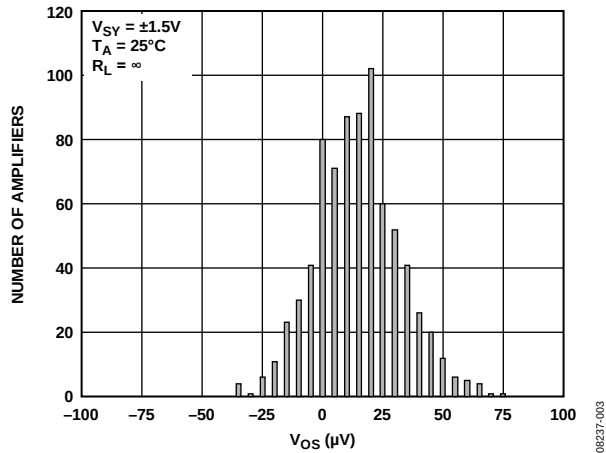


Figure 6. Input Offset Voltage (V_{OS}) Distribution, SOIC

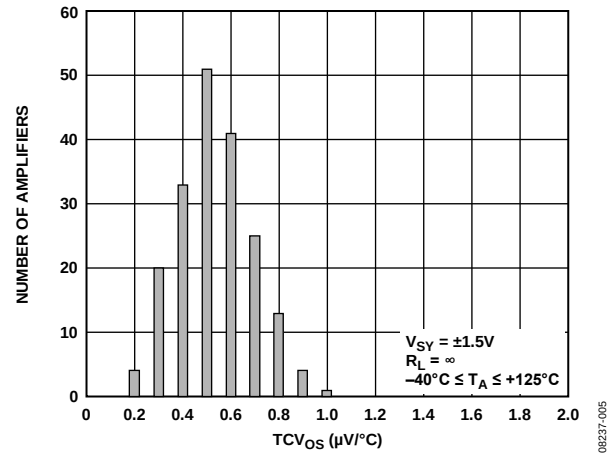


Figure 9. TCV_{OS} Distribution, SOIC, MSOP, and TSSOP

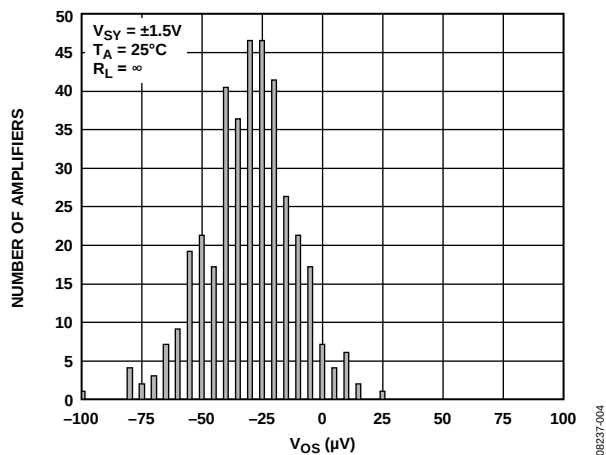


Figure 7. Input Offset Voltage (V_{OS}) Distribution, MSOP and TSSOP

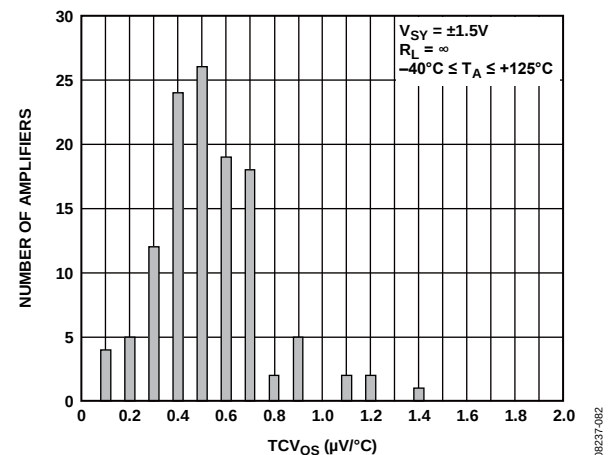


Figure 10. TCV_{OS} Distribution, LFCSP

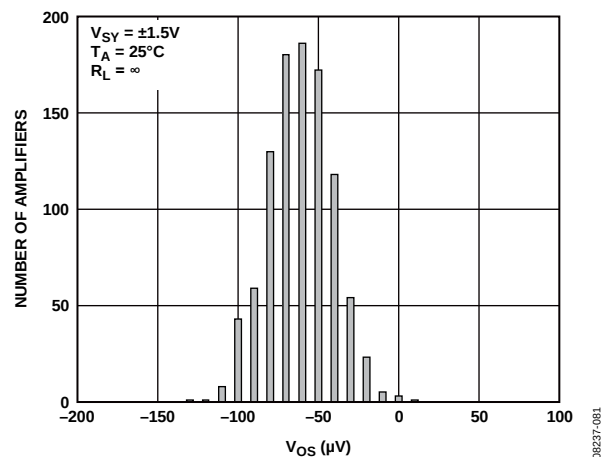


Figure 8. Input Offset Voltage (V_{OS}) Distribution, LFCSP

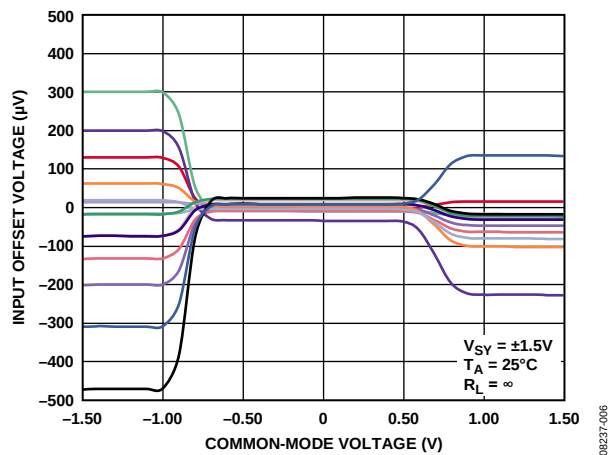


Figure 11. Input Offset Voltage vs. Common-Mode Voltage

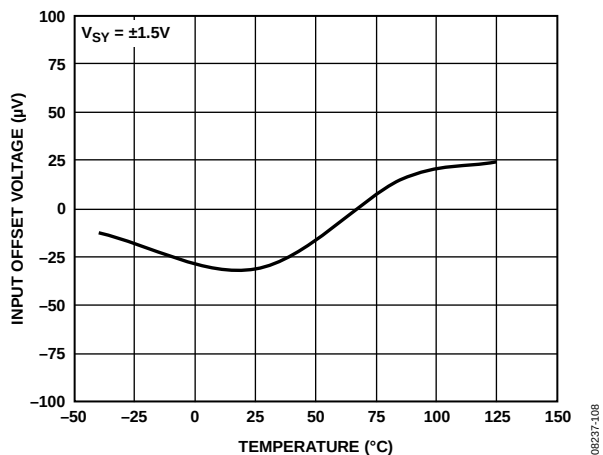


Figure 12. Input Offset Voltage vs. Temperature

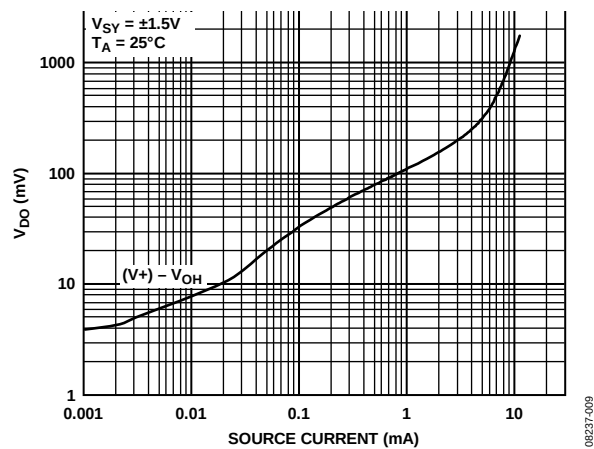
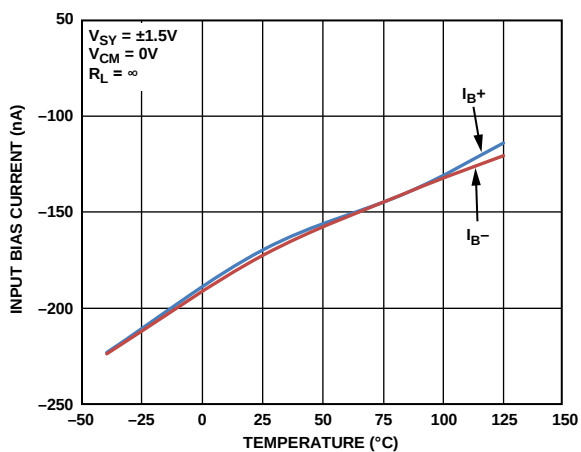
Figure 15. Dropout Voltage (V_{DO}) vs. Source Current

Figure 13. Input Bias Current vs. Temperature

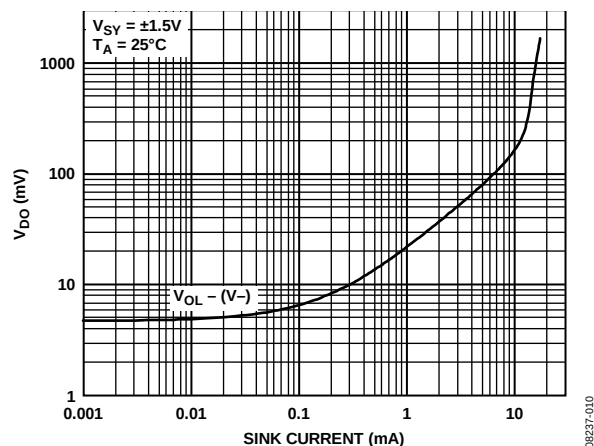
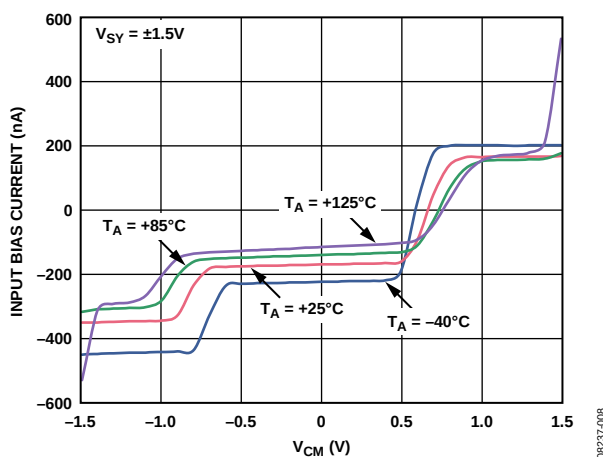
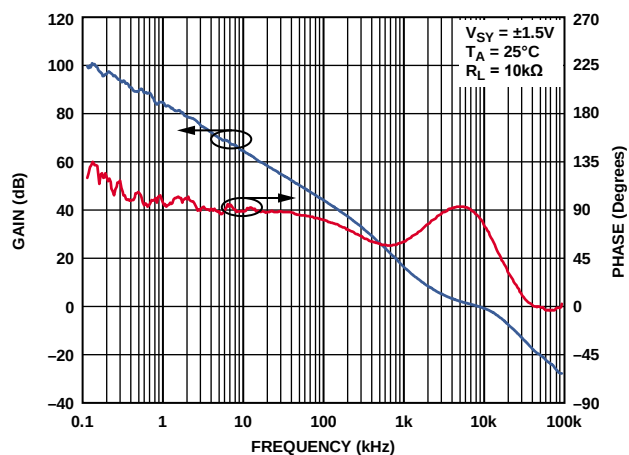
Figure 16. Dropout Voltage (V_{DO}) vs. Sink CurrentFigure 14. Input Bias Current vs. V_{CM} for Various Temperatures

Figure 17. Open-Loop Gain and Phase vs. Frequency

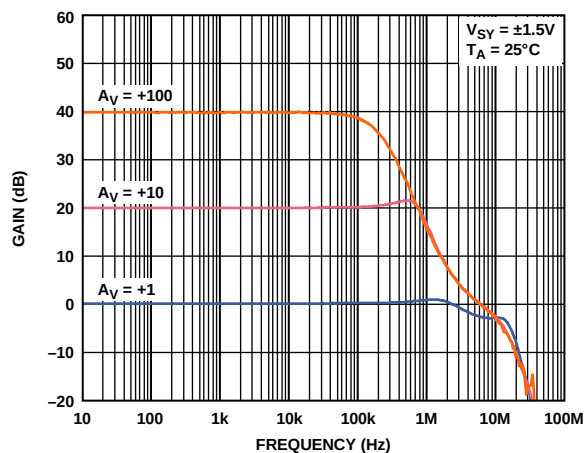


Figure 18. Closed-Loop Gain vs. Frequency

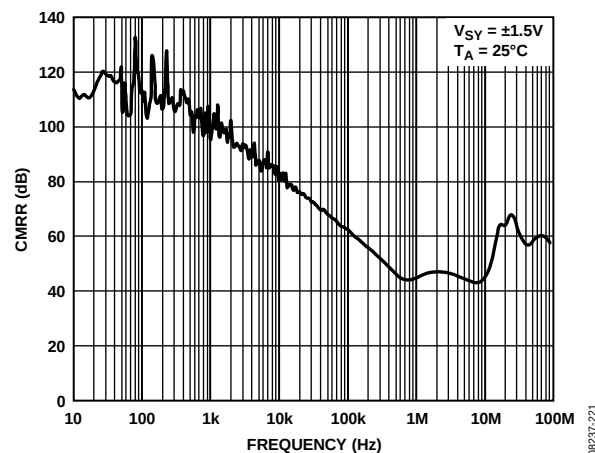


Figure 21. CMRR vs. Frequency

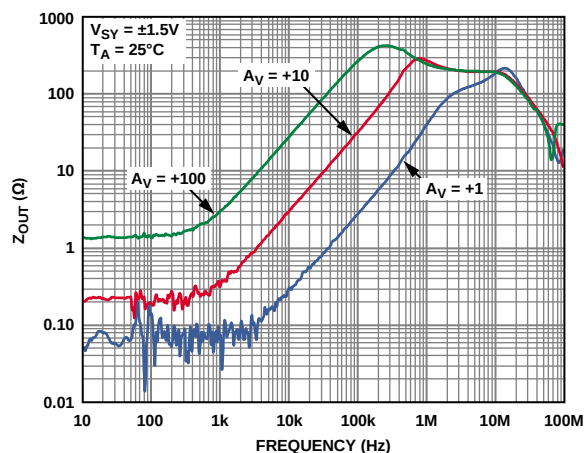


Figure 19. Output Impedance (Z_{OUT}) vs. Frequency

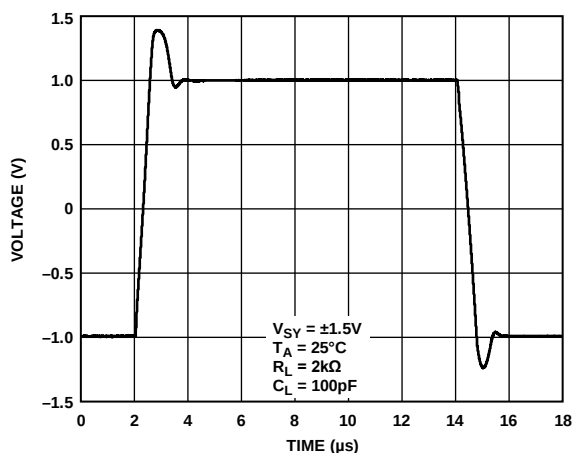


Figure 22. Large Signal Transient Response

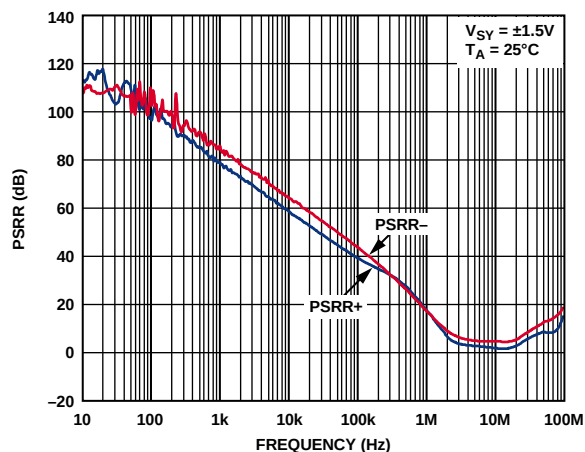


Figure 20. PSRR vs. Frequency

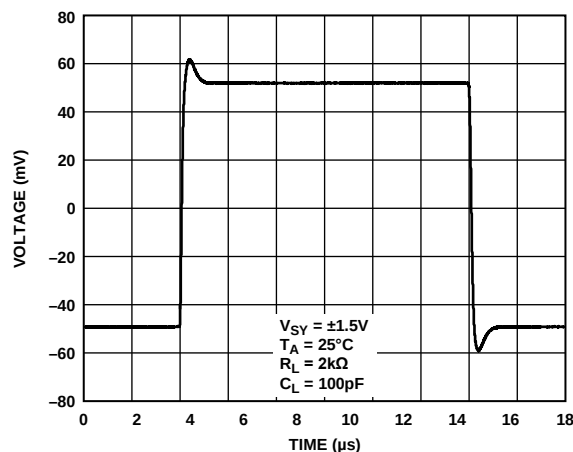


Figure 23. Small Signal Transient Response

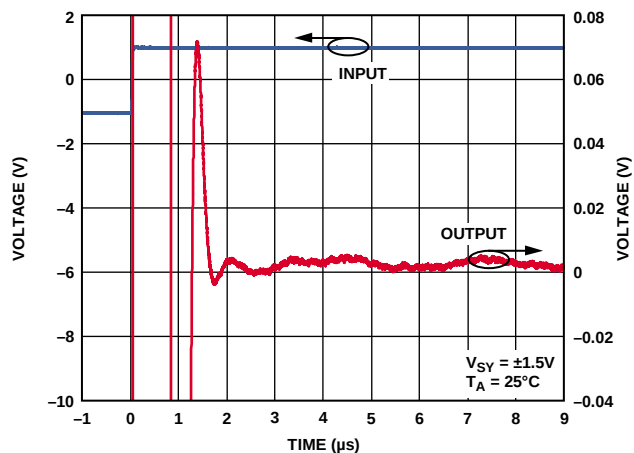


Figure 24. Settling Time

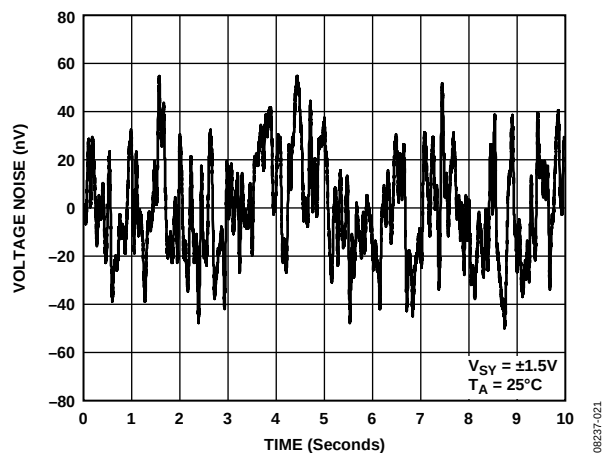


Figure 27. Voltage Noise, 0.1 Hz to 10 Hz

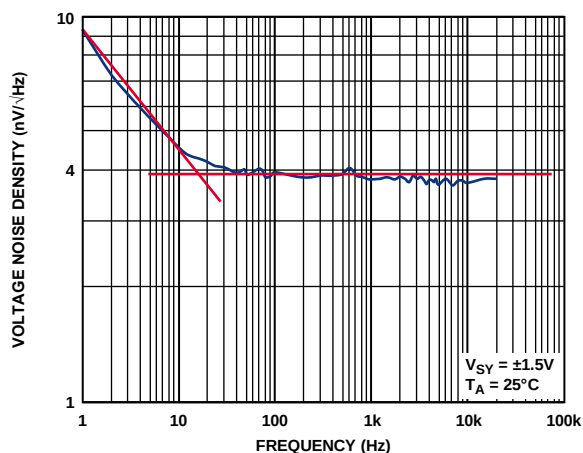


Figure 25. Voltage Noise Density vs. Frequency

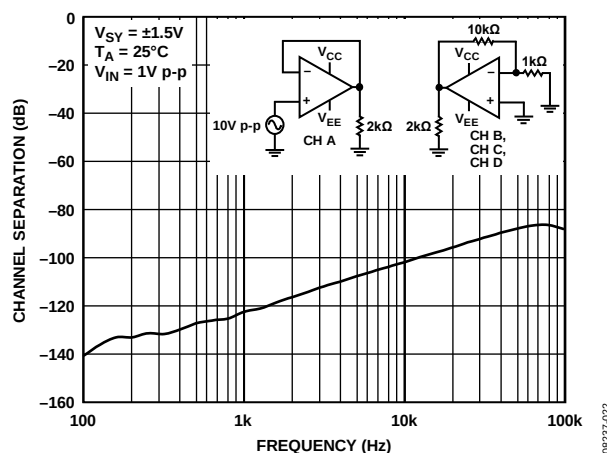


Figure 28. Channel Separation vs. Frequency

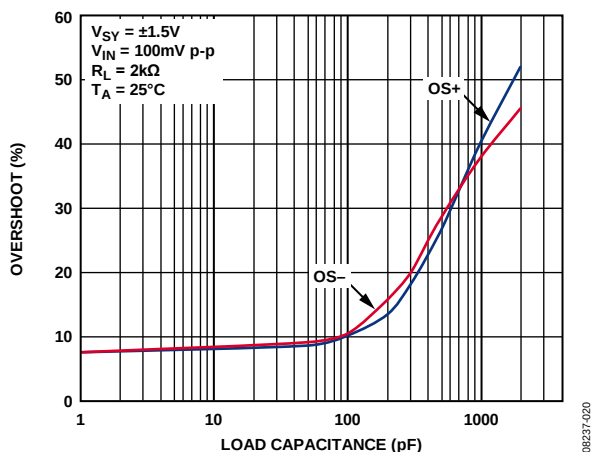


Figure 26. Overshoot vs. Load Capacitance

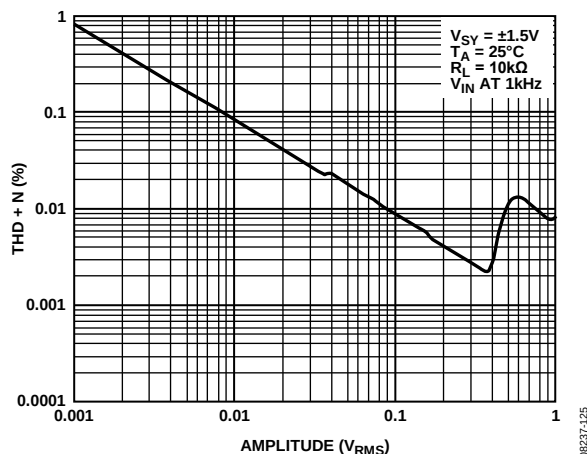


Figure 29. THD + N vs. Amplitude

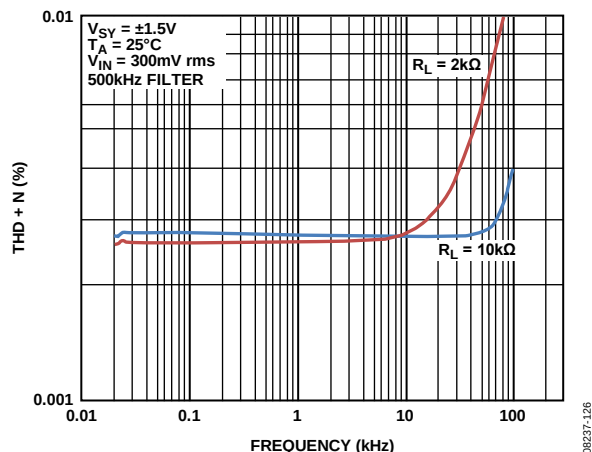


Figure 30. THD + N vs. Frequency, 500 kHz Filter

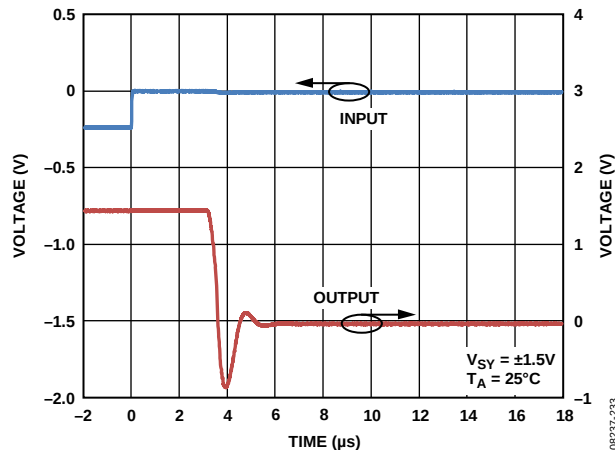


Figure 33. Positive 50% Overload Recovery

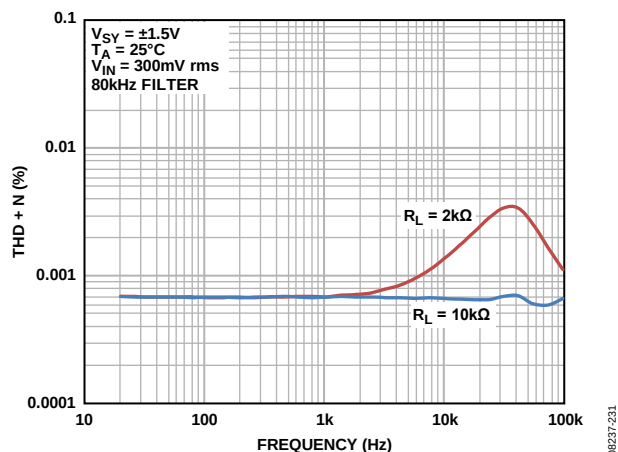


Figure 31. THD + N vs. Frequency, 80 kHz Filter

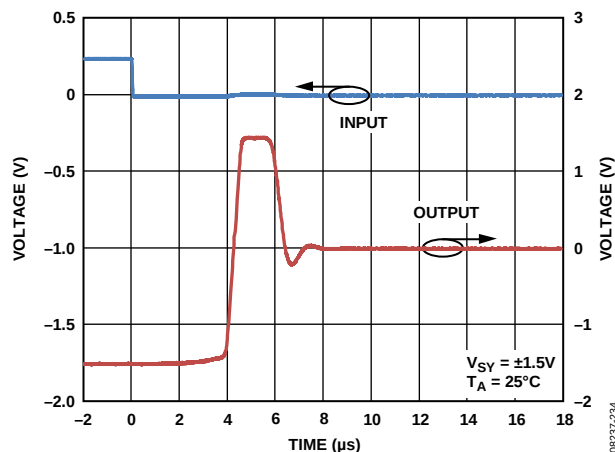


Figure 34. Negative 50% Overload Recovery

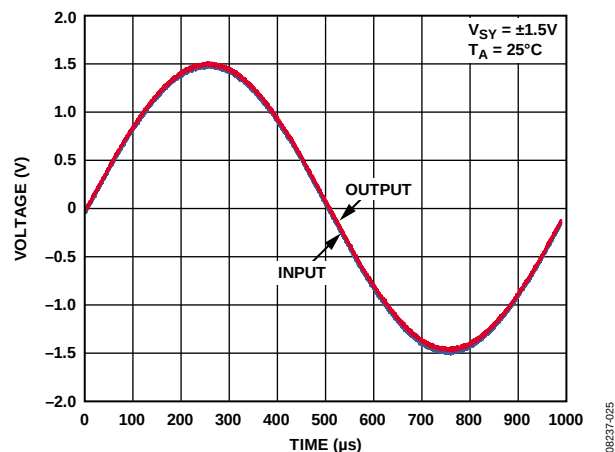


Figure 32. No Phase Reversal

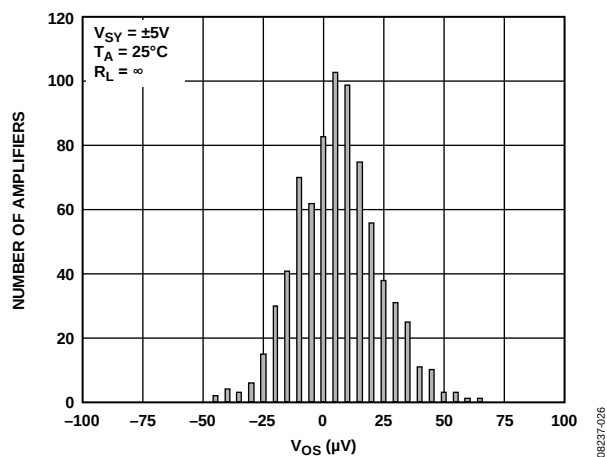
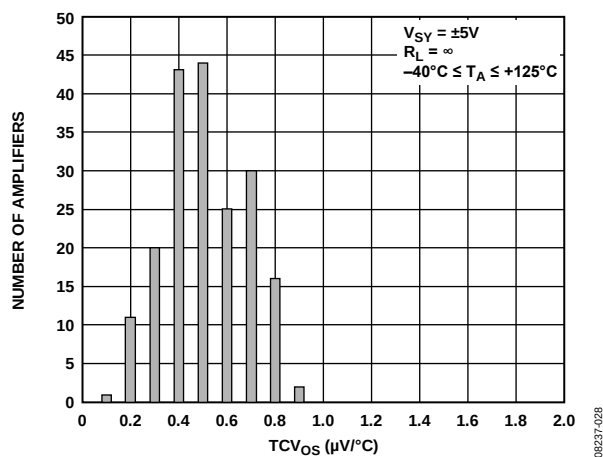
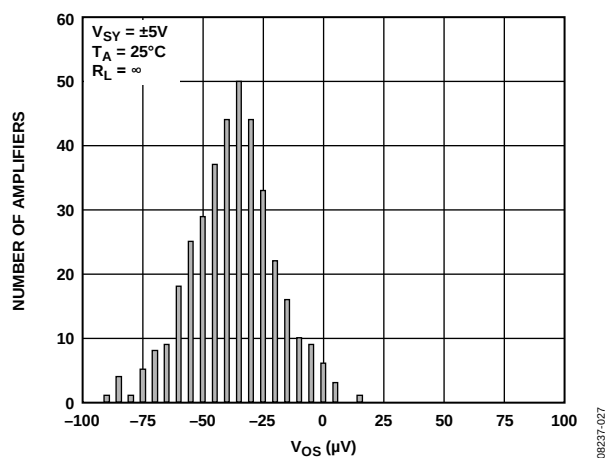
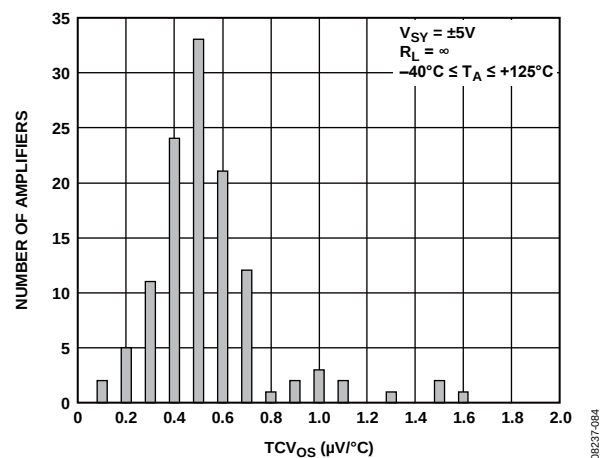
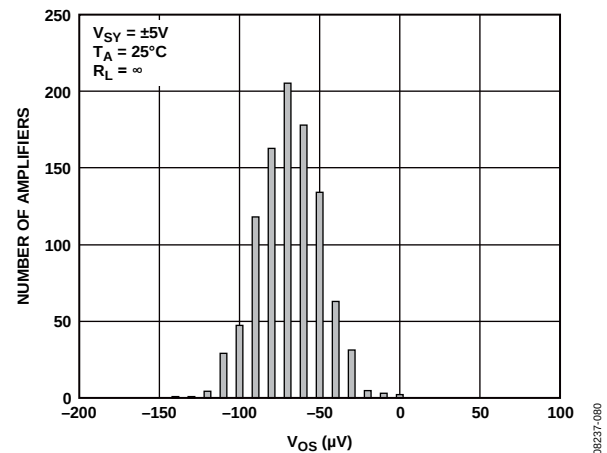
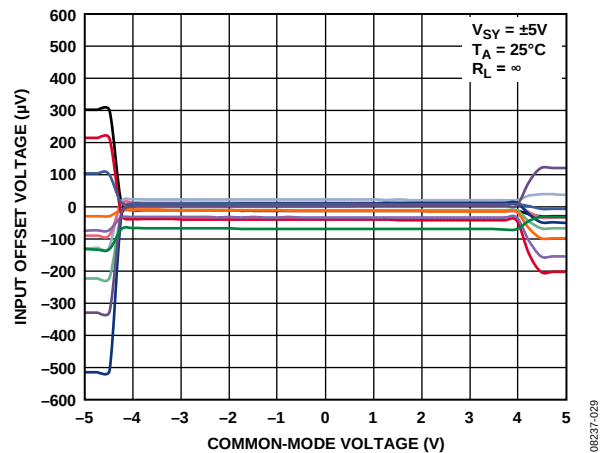
±5 V CHARACTERISTICSFigure 35. Input Offset Voltage (V_{OS}) Distribution, SOICFigure 38. TCV_{OS} Distribution, SOIC, MSOP, and TSSOPFigure 36. Input Offset Voltage (V_{OS}) Distribution, MSOP and TSSOPFigure 39. TCV_{OS} Distribution, LFCSPFigure 37. Input Offset Voltage (V_{OS}) Distribution, LFCSP

Figure 40. Input Offset Voltage vs. Common-Mode Voltage

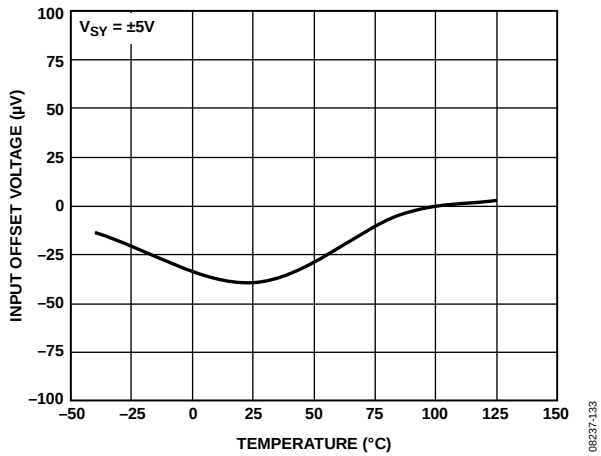


Figure 41. Input Offset Voltage vs. Temperature

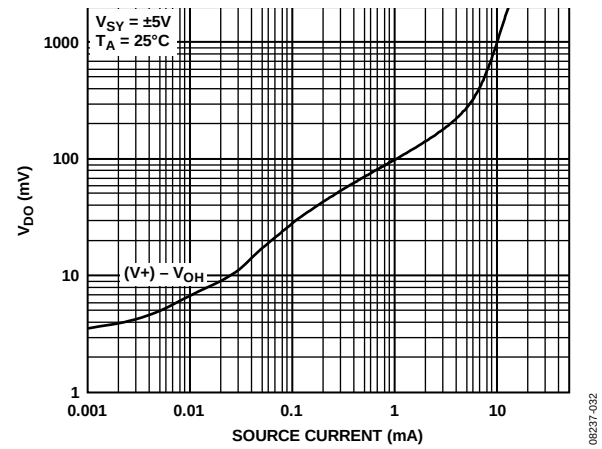


Figure 44. Dropout Voltage (V_{DO}) vs. Source Current

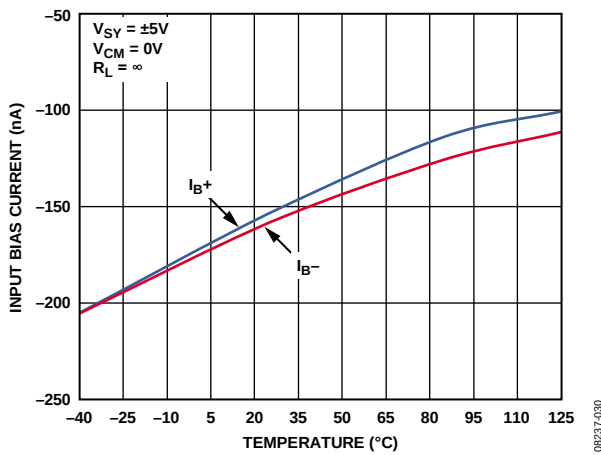


Figure 42. Input Bias Current vs. Temperature

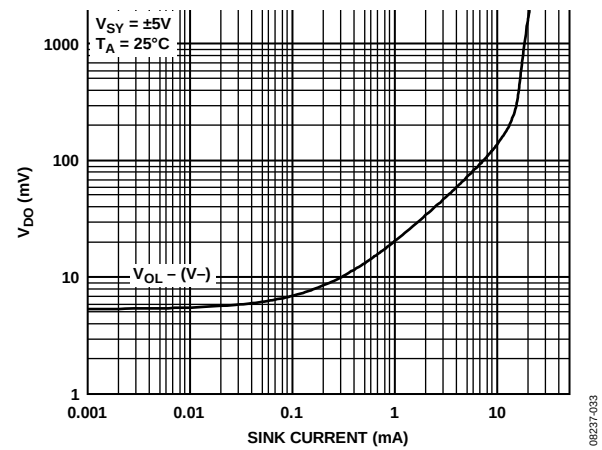


Figure 45. Dropout Voltage (V_{DO}) vs. Sink Current

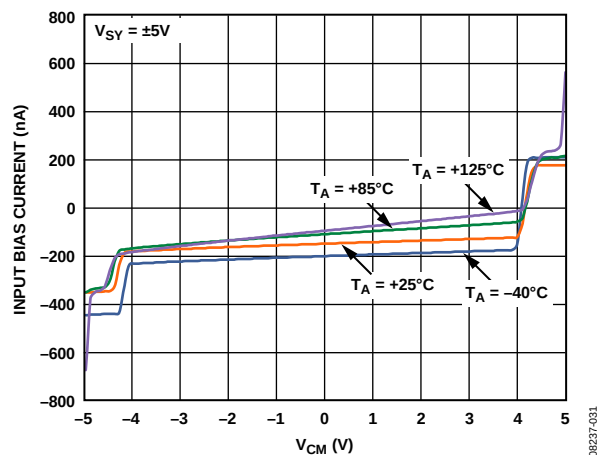


Figure 43. Input Bias Current vs. V_{CM} for Various Temperatures

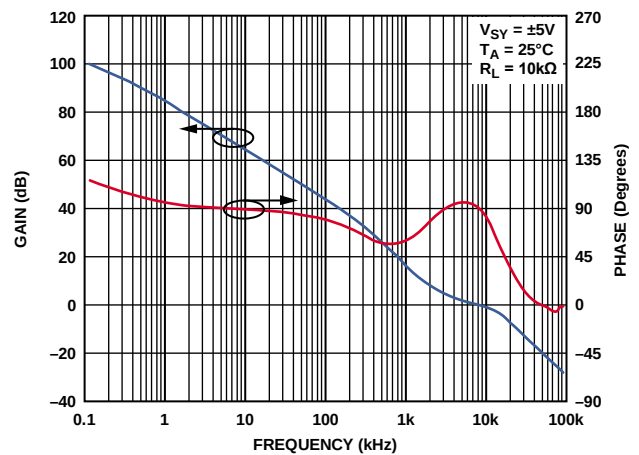


Figure 46. Open-Loop Gain and Phase vs. Frequency

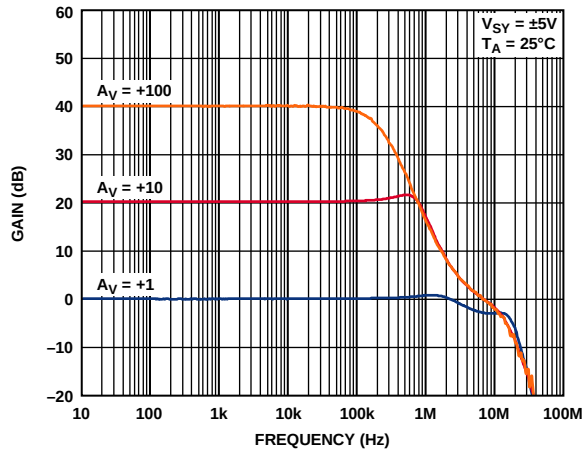


Figure 47. Closed-Loop Gain vs. Frequency

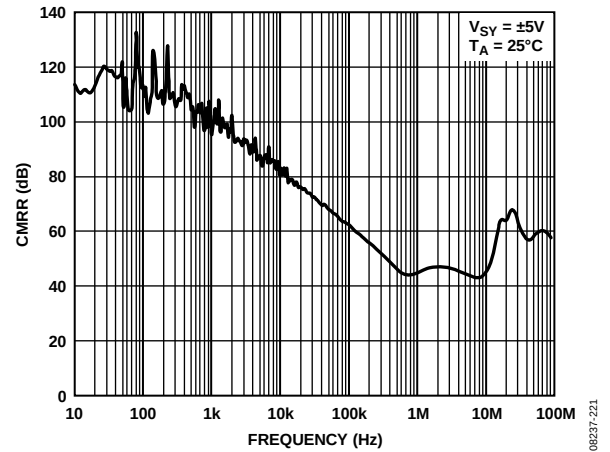


Figure 50. CMRR vs. Frequency

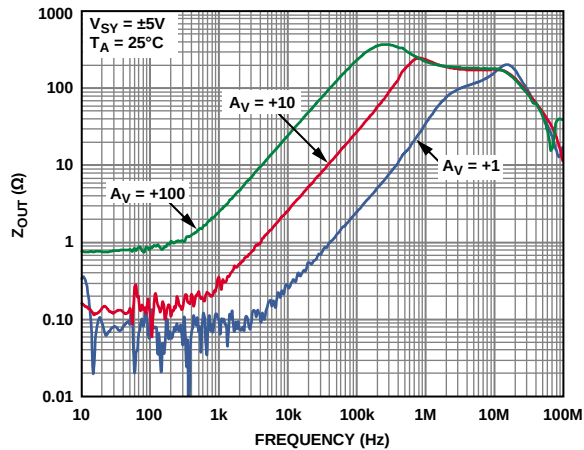
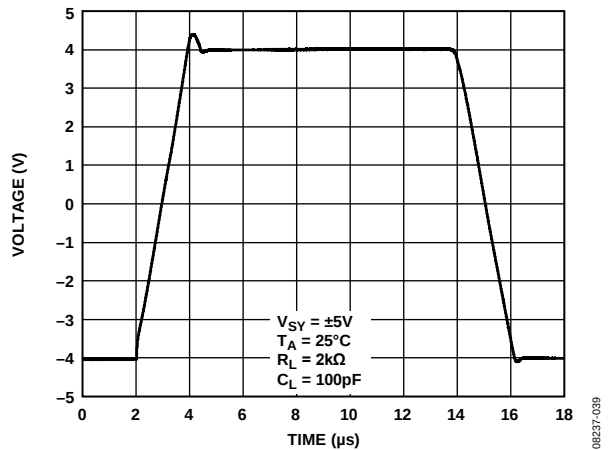
Figure 48. Output Impedance (Z_{OUT}) vs. Frequency

Figure 51. Large Signal Transient Response

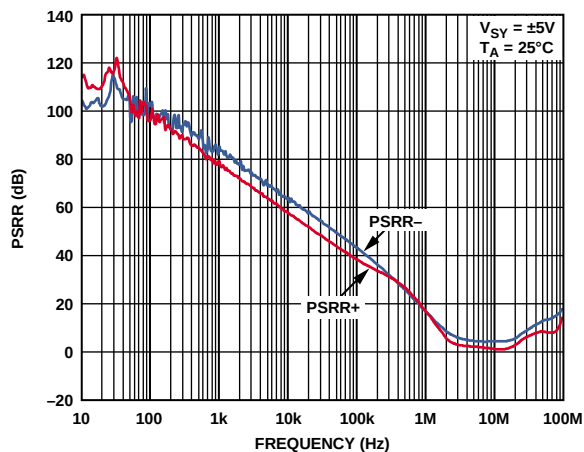


Figure 49. PSRR vs. Frequency

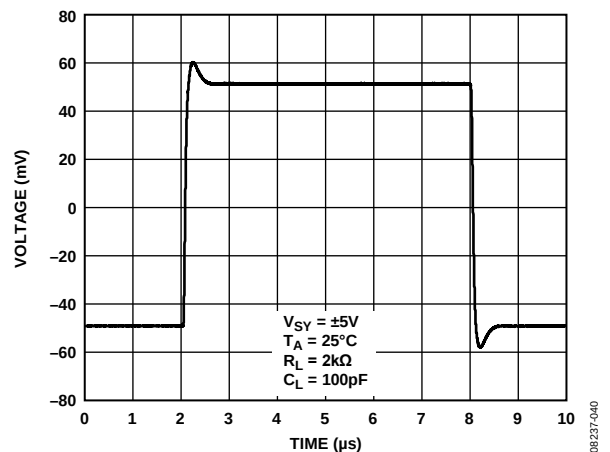


Figure 52. Small Signal Transient Response

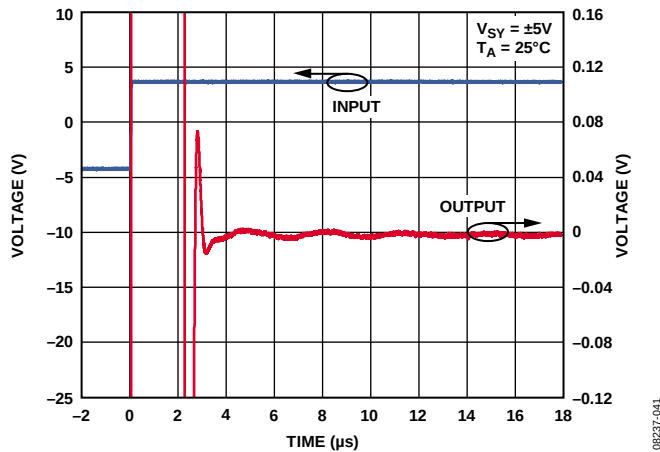


Figure 53. Settling Time

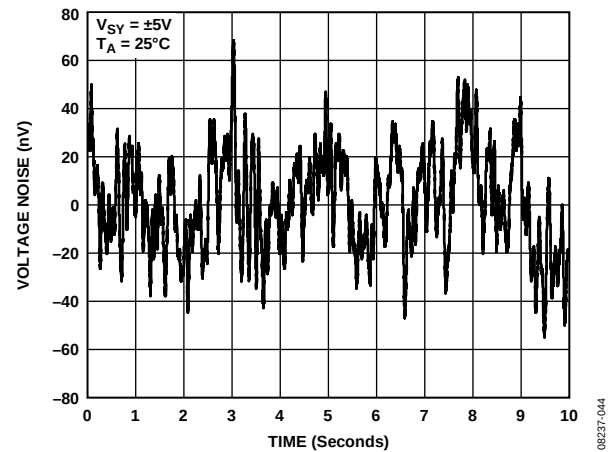


Figure 56. Voltage Noise, 0.1 Hz to 10 Hz

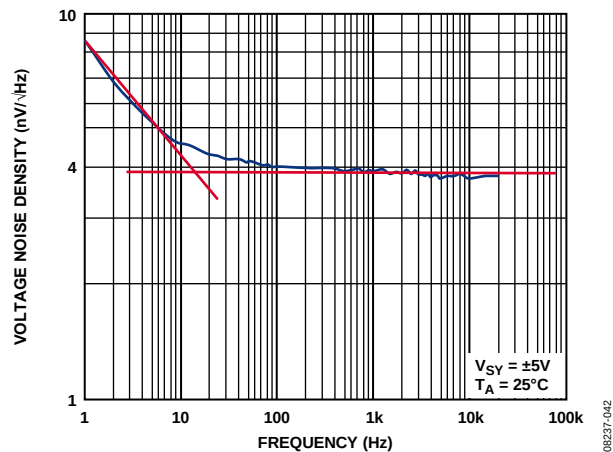


Figure 54. Voltage Noise Density vs. Frequency

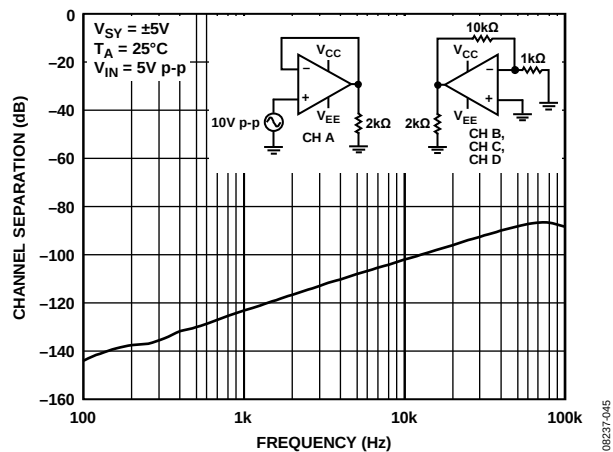


Figure 57. Channel Separation vs. Frequency

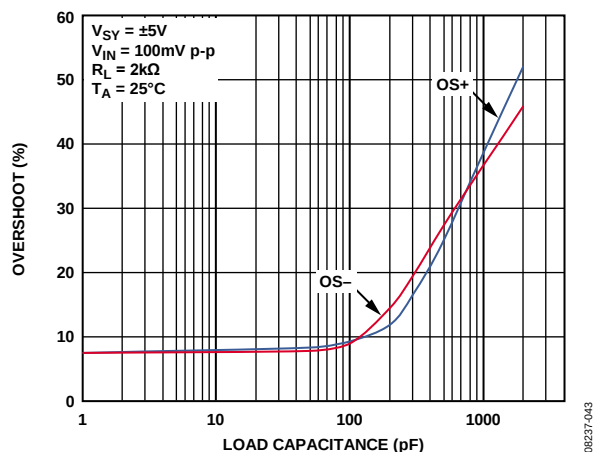


Figure 55. Overshoot vs. Load Capacitance

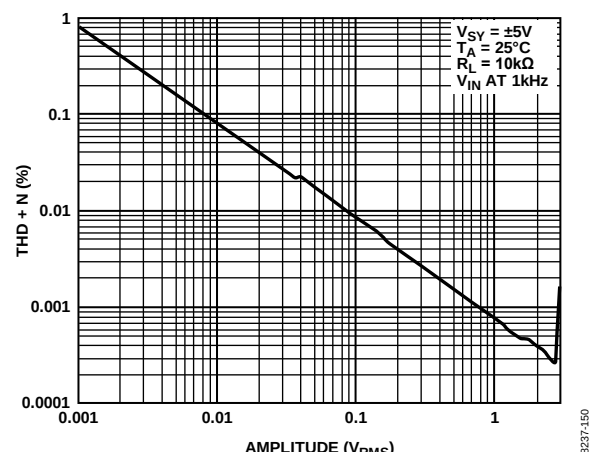


Figure 58. THD + N vs. Amplitude

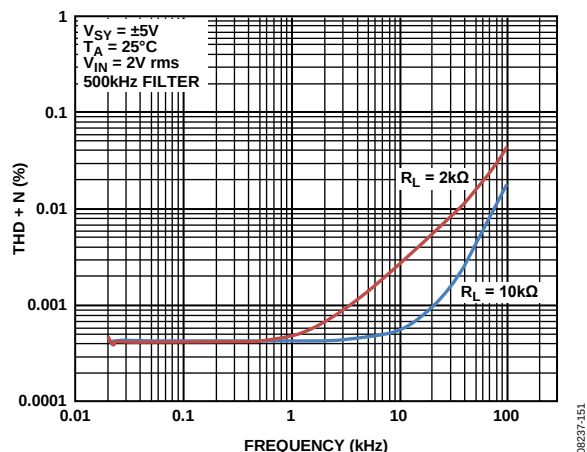


Figure 59. THD + N vs. Frequency, 500 kHz Filter

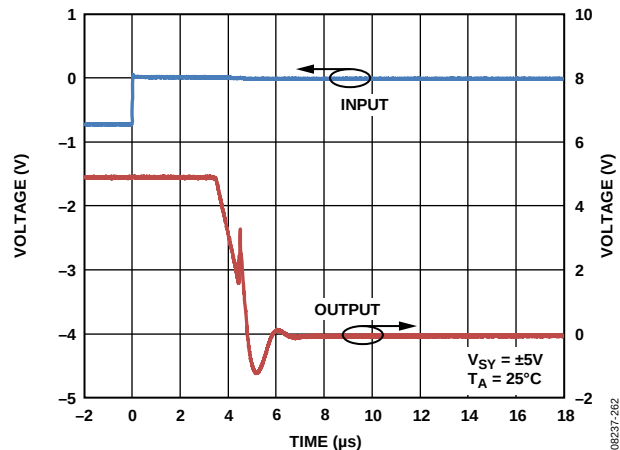


Figure 62. Positive 50% Overload Recovery

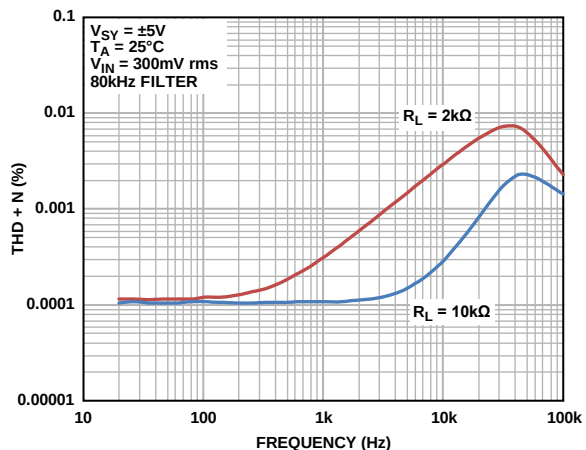


Figure 60. THD + N vs. Frequency, 80 kHz Filter

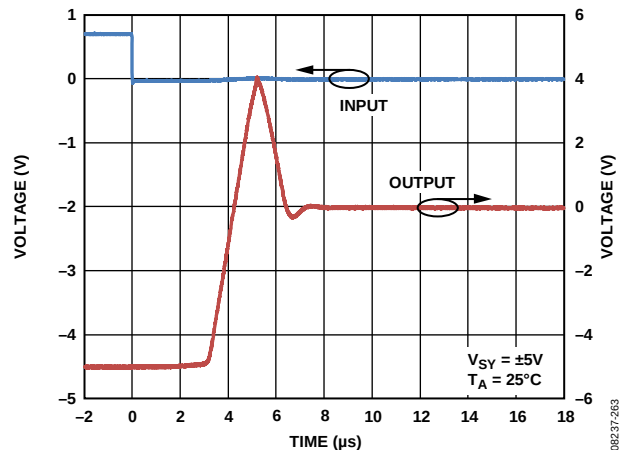


Figure 63. Negative 50% Overload Recovery

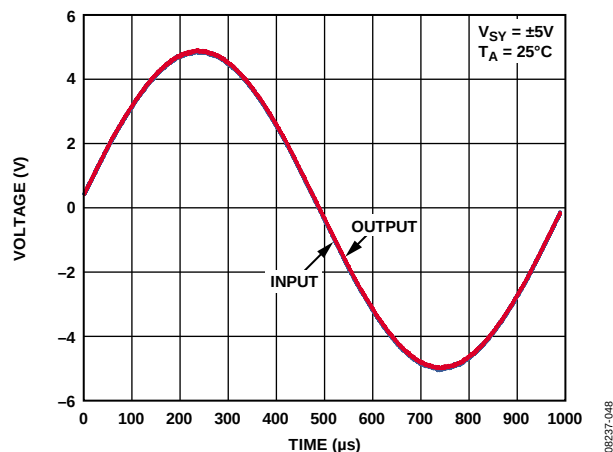


Figure 61. No Phase Reversal

±15 V CHARACTERISTICS

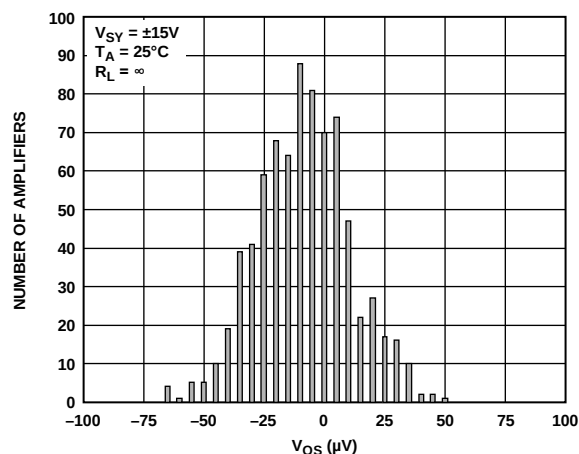


Figure 64. Input Offset Voltage (V_{OS}) Distribution, SOIC

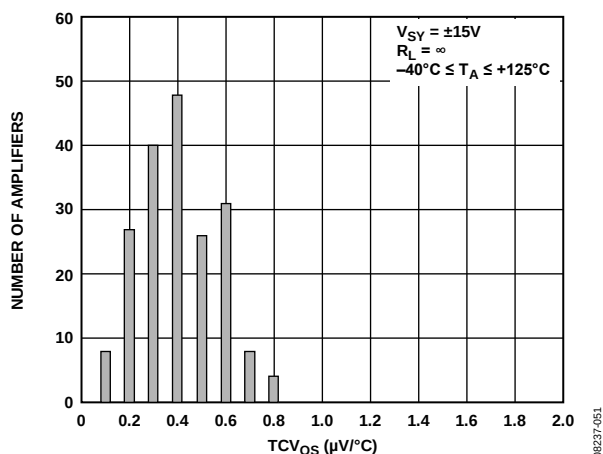


Figure 67. TCV_{OS} Distribution, SOIC, MSOP, and TSSOP

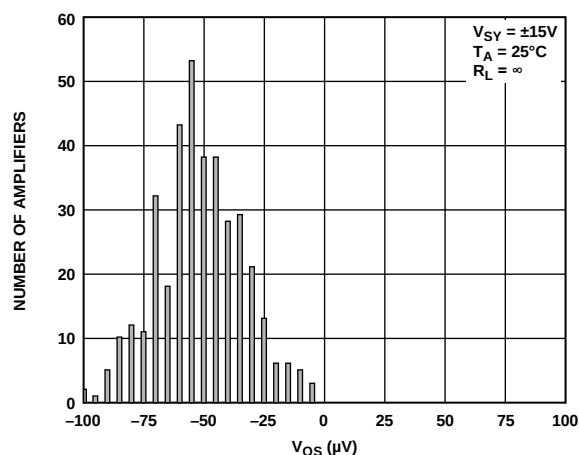


Figure 65. Input Offset Voltage (V_{OS}) Distribution, MSOP and TSSOP

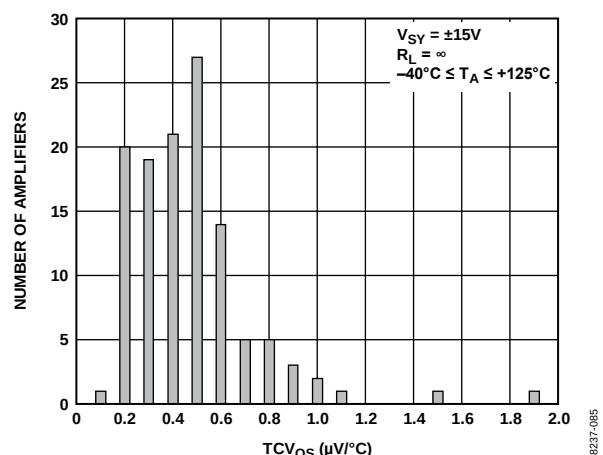


Figure 68. TCV_{OS} Distribution, LFCSP

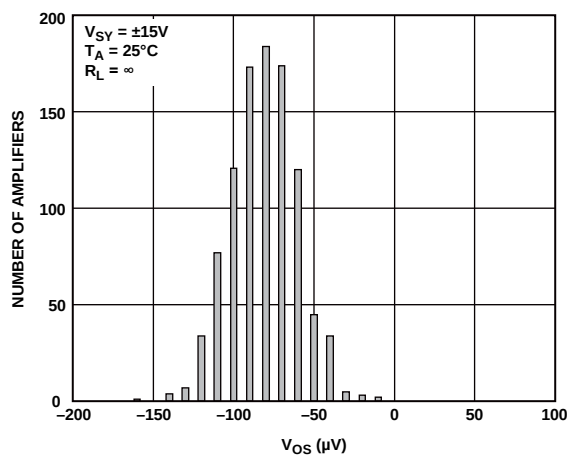


Figure 66. Input Offset Voltage (V_{OS}) Distribution, LFCSP

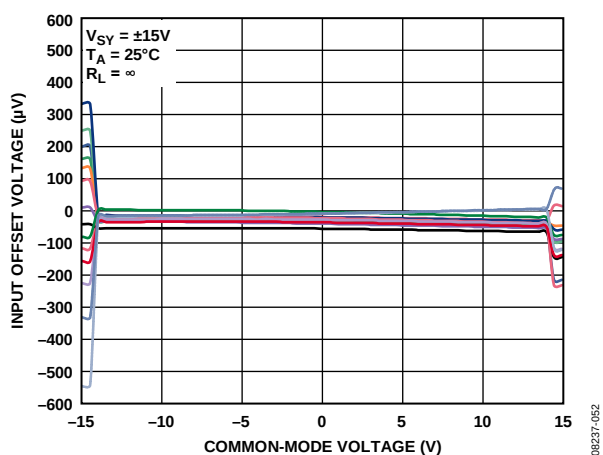


Figure 69. Input Offset Voltage vs. Common-Mode Voltage

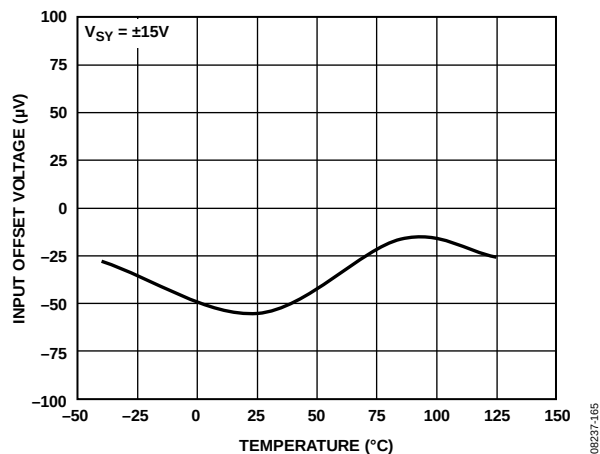


Figure 70. Input Offset Voltage vs. Temperature

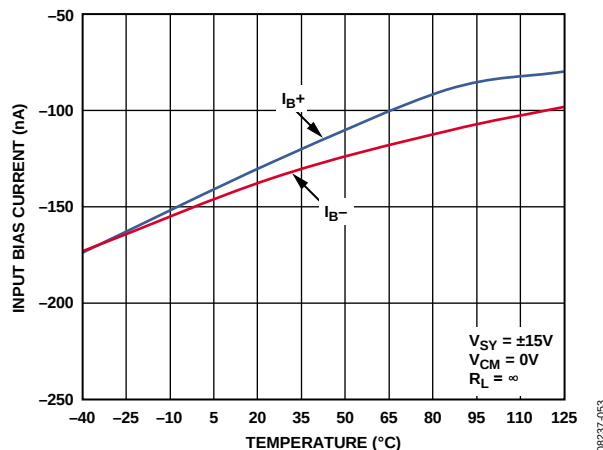


Figure 71. Input Bias Current vs. Temperature

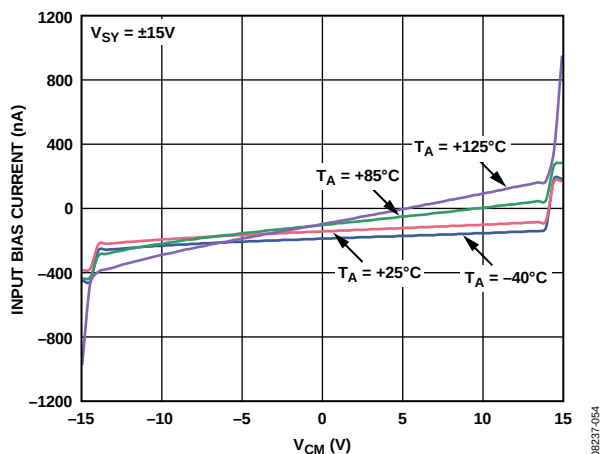
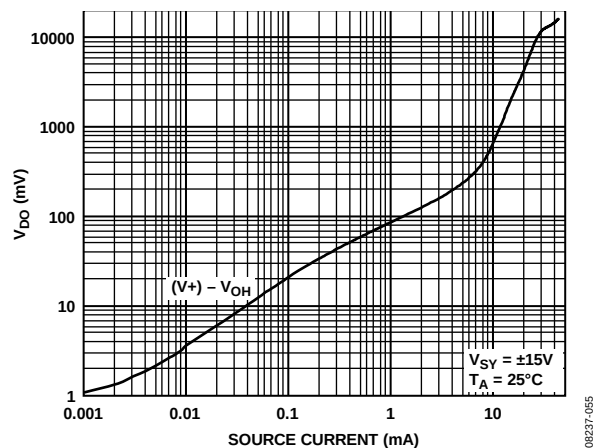
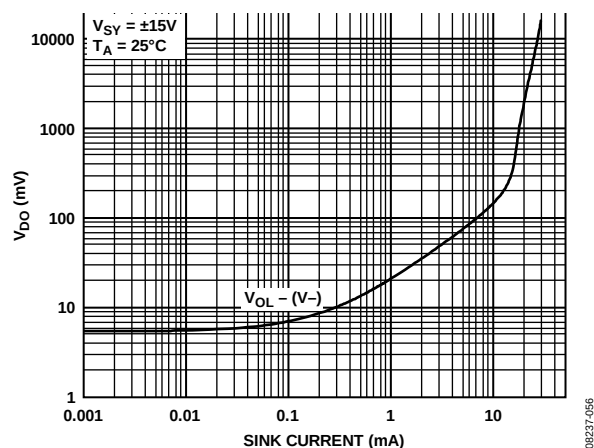
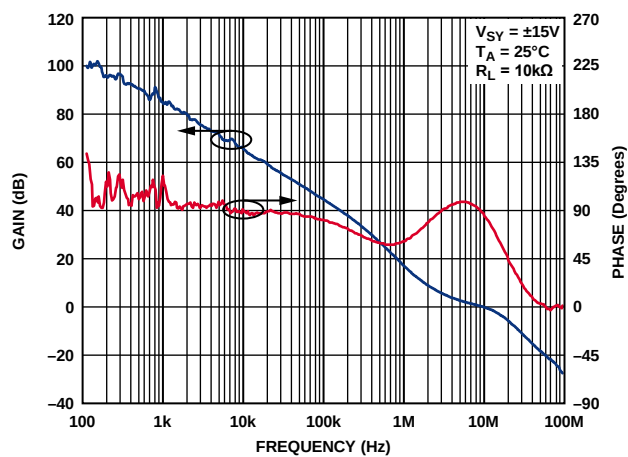
Figure 72. Input Bias Current vs. V_{CM} for Various TemperaturesFigure 73. Dropout Voltage (V_{DO}) vs. Source CurrentFigure 74. Dropout Voltage (V_{DO}) vs. Sink Current

Figure 75. Open-Loop Gain and Phase vs. Frequency

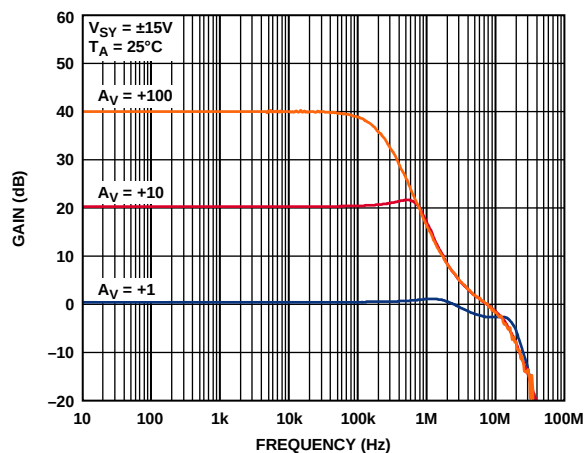


Figure 76. Closed-Loop Gain vs. Frequency

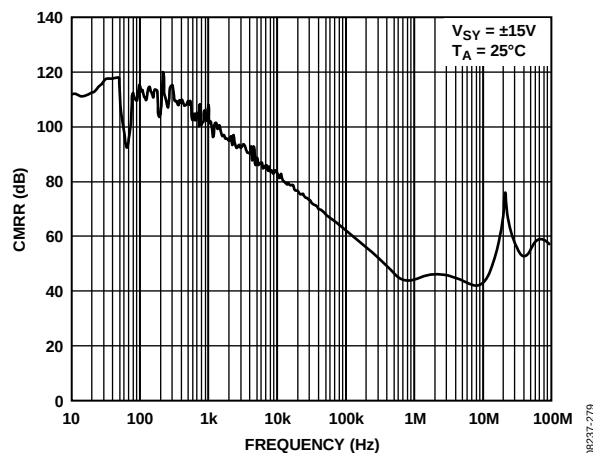


Figure 79. CMRR vs. Frequency

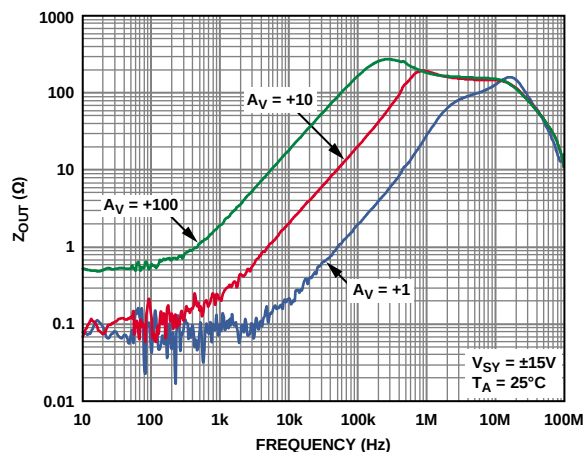


Figure 77. Output Impedance (Z_{OUT}) vs. Frequency

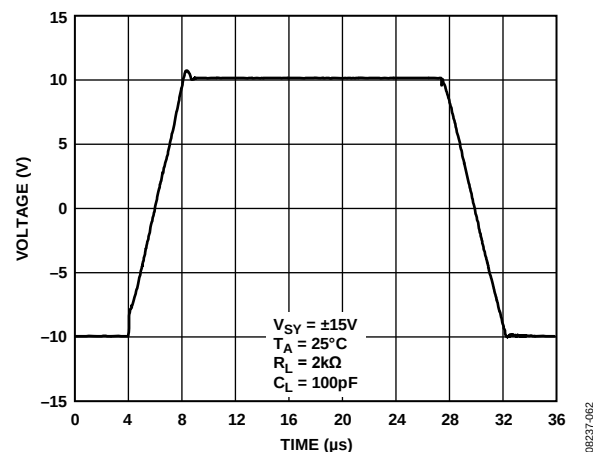


Figure 80. Large Signal Transient Response

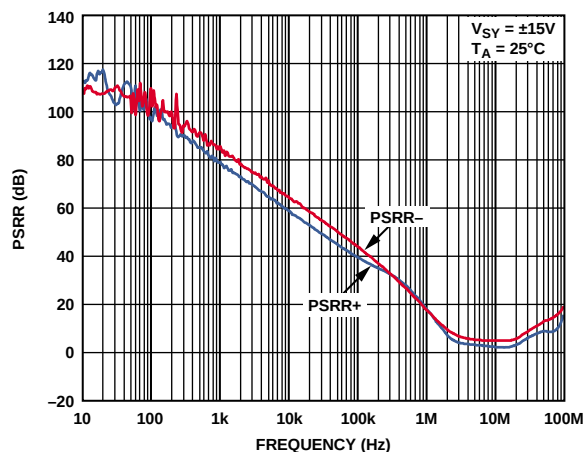


Figure 78. PSRR vs. Frequency

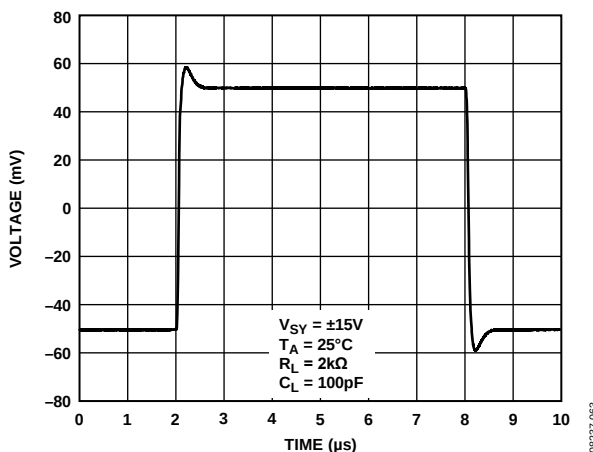


Figure 81. Small Signal Transient Response

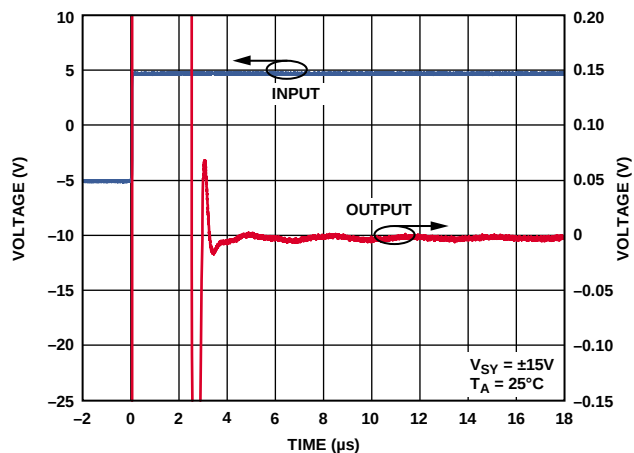


Figure 82. Settling Time

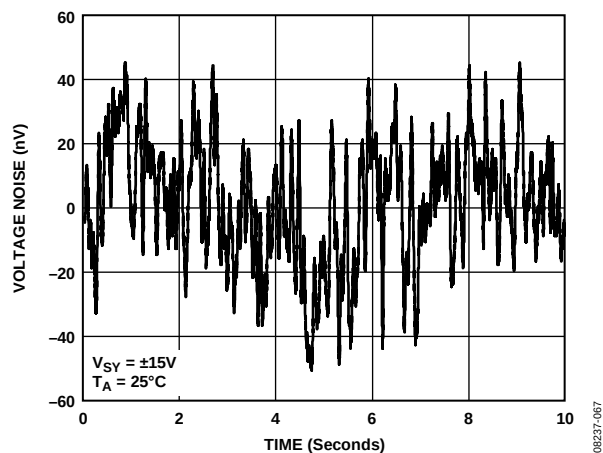


Figure 85. Voltage Noise 0.1 Hz to 10 Hz

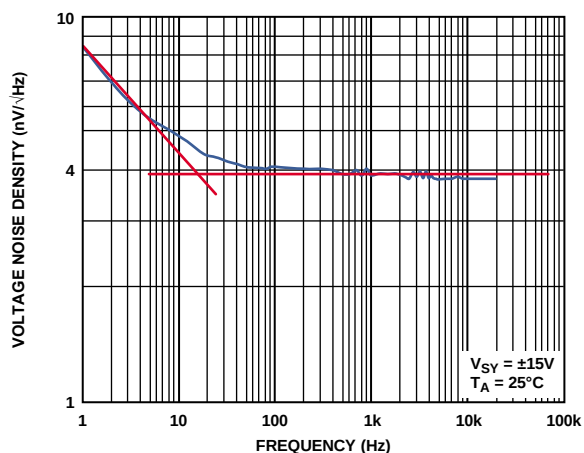


Figure 83. Voltage Noise Density vs. Frequency

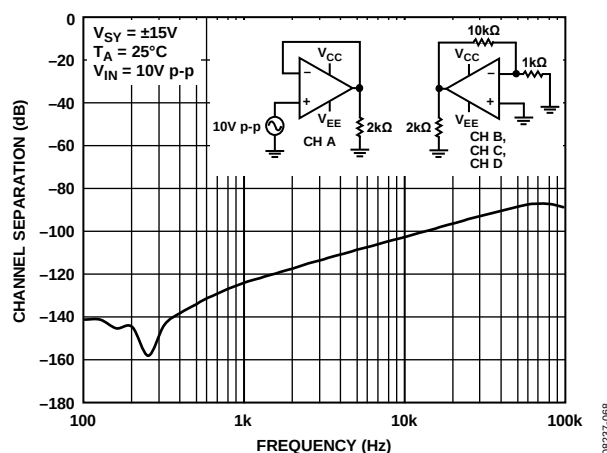


Figure 86. Channel Separation vs. Frequency

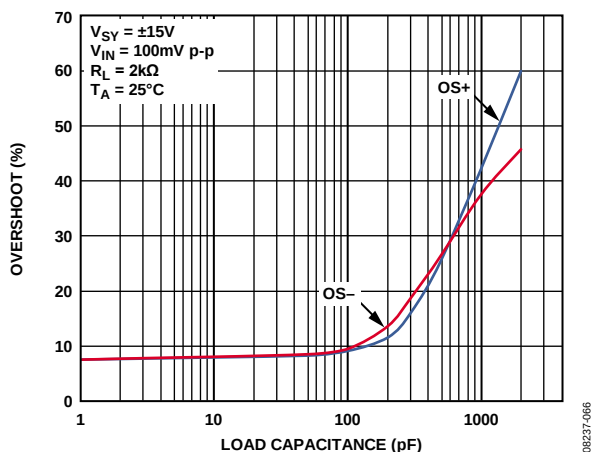


Figure 84. Overshoot vs. Load Capacitance

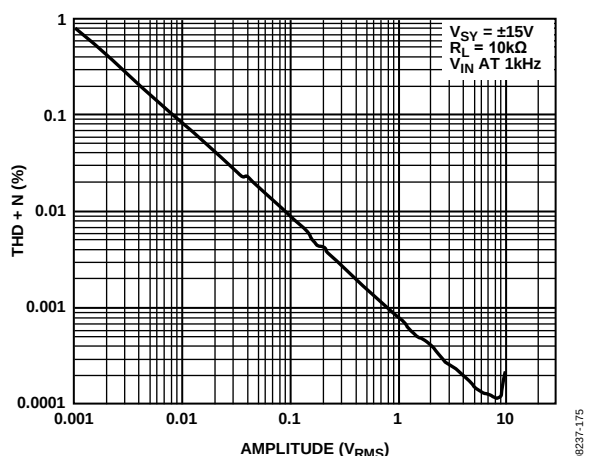


Figure 87. THD + N vs. Amplitude

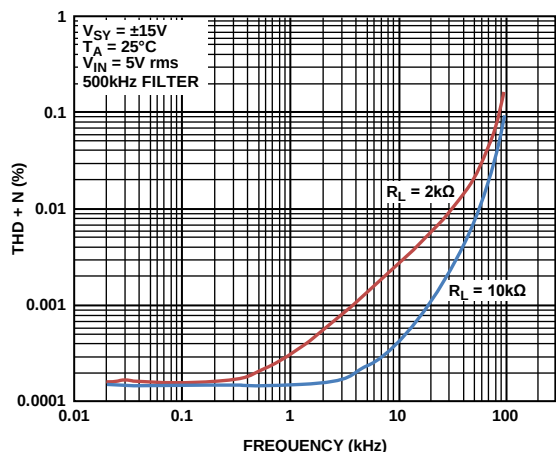


Figure 88. THD + N vs. Frequency, 500 kHz Filter

08237-176

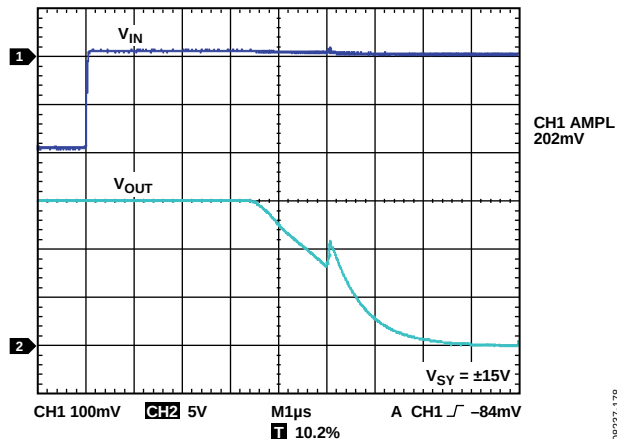


Figure 91. Positive 50% Overload Recovery

08237-178

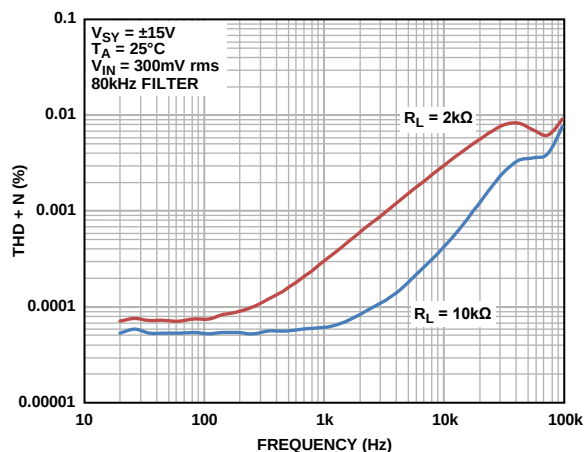


Figure 89. THD + N vs. Frequency, 80 kHz Filter

08237-289

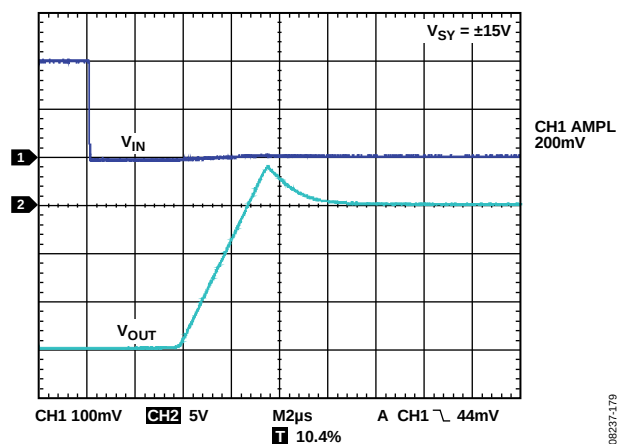


Figure 92. Negative 50% Overload Recovery

08237-179

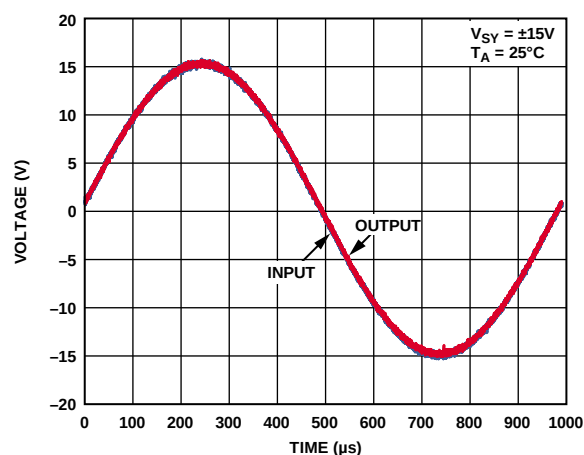


Figure 90. No Phase Reversal

08237-071

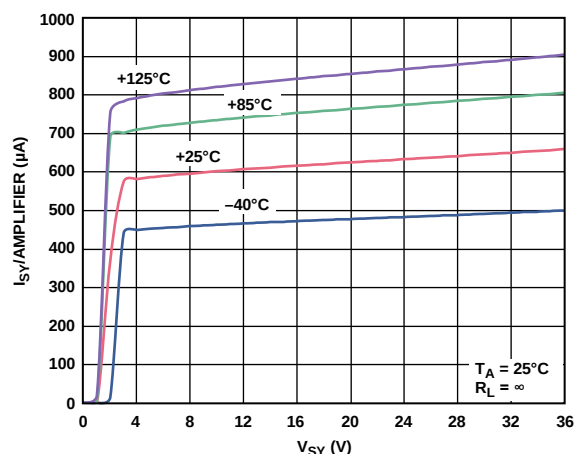


Figure 93. Supply Current (I_{SY}) per Amplifier vs. Supply Voltage (V_{SY}) for Various Temperatures

08237-072

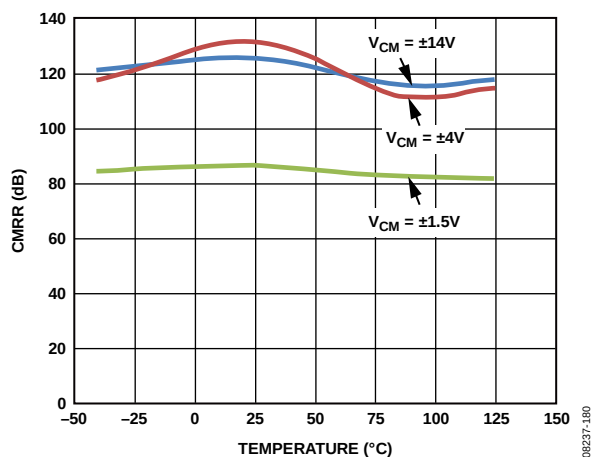


Figure 94. CMRR vs. Temperature

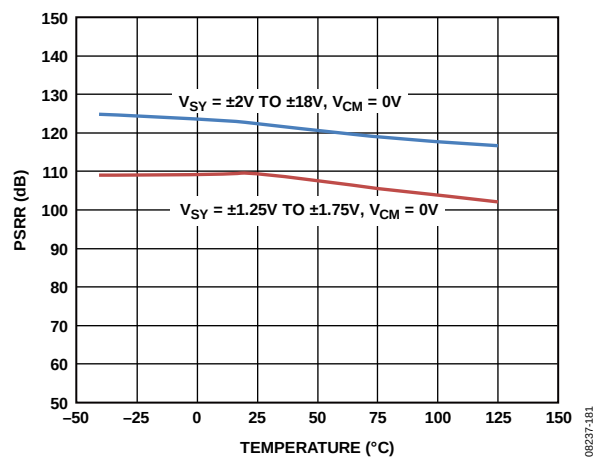


Figure 95. PSRR vs. Temperature

APPLICATIONS INFORMATION

FUNCTIONAL DESCRIPTION

The ADA4084-1/ADA4084-2/ADA4084-4 devices are precision single-supply, rail-to-rail operational amplifiers. Intended for portable instrumentation, the ADA4084-1/ADA4084-2/ADA4084-4 devices combine the attributes of precision, wide bandwidth, and low noise, making them an ideal choice in single-supply applications that require both ac and precision dc performance. Other low supply voltage applications for which the ADA4084-1/ADA4084-2/ADA4084-4 devices are well suited include active filters, audio microphone preamplifiers, power supply control, and telecommunications. To combine all of these attributes with rail-to-rail input/output operation, novel circuit design techniques are used.

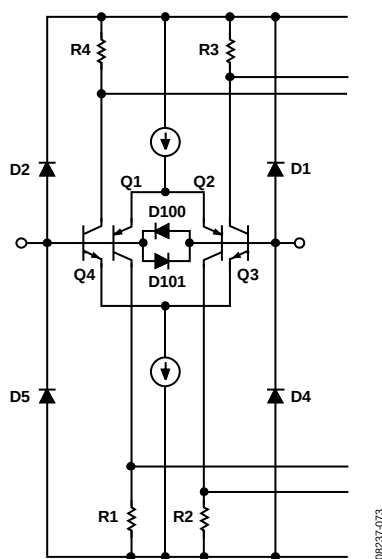


Figure 96. Equivalent Input Circuit

For example, Figure 96 illustrates a simplified equivalent circuit for the input stage of the ADA4084-1/ADA4084-2/ADA4084-4. It comprises a PNP differential pair, Q1 and Q2, and an NPN differential pair, Q3 and Q4, operating concurrently. Diode D100 and Diode D101 serve to clamp the applied differential input voltage to the ADA4084-1/ADA4084-2/ADA4084-4, thereby protecting the input transistors against Zener breakdown of the emitter-base junctions. Input stage voltage gains are kept low for input rail-to-rail operation. The two pairs of differential output voltages are connected to the second stage of the ADA4084-1/ADA4084-2/ADA4084-4, which is a modified compound folded cascade gain stage. It is also in the second gain stage that the two pairs of differential output voltages are combined into a single-ended output signal voltage used to drive the output stage.

A key issue in the input stage is the behavior of the input bias currents over the input common-mode voltage range. Input bias currents in the ADA4084-1/ADA4084-2/ADA4084-4 are the arithmetic sum of the base currents in Q1 and Q4 and in Q2 and Q3. As a result, of this design approach, the input bias currents in the ADA4084-1/ADA4084-2/ADA4084-4 not only exhibit different amplitudes but they also exhibit different polarities. This effect is best illustrated by Figure 13, Figure 14, Figure 42, Figure 43, Figure 71, and Figure 72. It is, therefore, important that the effective source impedances that are connected to the ADA4084-1/ADA4084-2/ADA4084-4 inputs be balanced for optimum dc and ac performance.

To achieve rail-to-rail output, the ADA4084-1/ADA4084-2/ADA4084-4 output stage design employs a unique topology for both sourcing and sinking current. This circuit topology is shown in Figure 97. The output stage is voltage driven from the second gain stage. The signal path through the output stage is inverting; that is, for positive input signals, Q13 provides the base current drive to Q19 so that it conducts (sinks) current. For negative input signals, the signal path via Q18 → mirror → Q24 provides the base current drive for Q23 to conduct (source) current. Both transistors provide output current until they are forced into saturation.

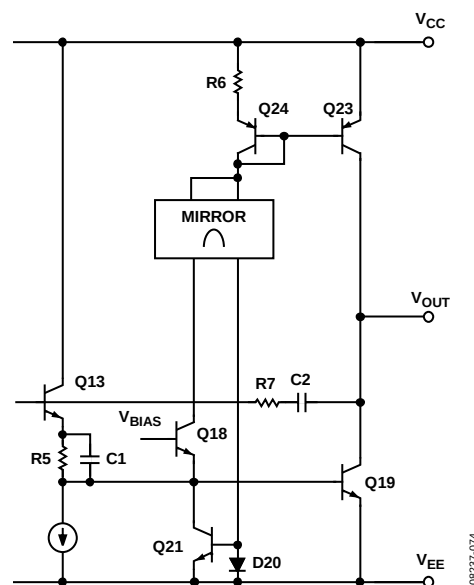


Figure 97. Equivalent Output Circuit

Thus, the saturation voltage of the output transistors sets the limit on the ADA4084-1/ADA4084-2/ADA4084-4 maximum output voltage swing. Output short-circuit current limiting is determined by the maximum signal current into the base of Q13 from the second gain stage. The output stage also exhibits voltage gain. This is accomplished by the use of common-emitter amplifiers, and, as a result, the voltage gain of the output stage (thus, the open-loop gain of the device) exhibits a dependence on the total load resistance at the output of the ADA4084-1/ADA4084-2/ADA4084-4.

START-UP CHARACTERISTICS

The ADA4084-1/ADA4084-2/ADA4084-4 are specified to operate from 3 V to 30 V (± 1.5 V to ± 15 V) under nominal power supplies. During power-up as the supply voltage increases from 0 V to the nominal power supply voltage, the supply current (I_{SY}) increases as well, to the point at which it stabilizes and the amplifier is ready to operate. The stabilization varies with temperature, as shown in Figure 93. For example, at -40°C , it requires a higher voltage and stabilizes at a lower supply current than at hot temperatures. At hot temperatures, it requires a lower voltage but stabilizes at a higher current. In all cases, the ADA4084-1/ADA4084-2/ADA4084-4 are specified to start up and operate at a minimum of 3 V under all temperature conditions.

INPUT PROTECTION

As with any semiconductor device, if conditions exist where the applied input voltages to the device exceed either supply voltage, the input overvoltage I-to-V characteristic of the device must be considered. When an overvoltage occurs, the amplifier may be damaged, depending on the magnitude of the applied voltage and the magnitude of the fault current.

The D1, D2, D4, and D5 diodes conduct when the input common-mode voltage exceeds either supply pin by a diode drop. This diode drop voltage varies with temperature and is in the range of 0.3 V to 0.8 V. As shown in the simplified equivalent input circuit of Figure 96, the ADA4084-1/ADA4084-2/ADA4084-4 do not have any internal current limiting resistors; thus, fault currents can quickly rise to damaging levels.

This input current is not inherently damaging to the device, provided that it is limited to 5 mA or less. If a fault condition causes more than 5 mA to flow, add an external series resistor at the expense of additional thermal noise. Figure 98 shows a typical noninverting configuration for an overvoltage protected amplifier, where the series resistance ($R1$) is chosen, such that

$$R1 = \frac{V_{IN(MAX)} - V_{SUPPLY}}{5 \text{ mA}}$$

For example, a 1 k Ω resistor protects the ADA4084-1/ADA4084-2/ADA4084-4 against input signals up to 5 V above and below the supplies. Note that the thermal noise of a 1 k Ω resistor at room temperature is 4 nV/ $\sqrt{\text{Hz}}$, which exceeds the voltage noise of the ADA4084-1/ADA4084-2/ADA4084-4. For other configurations in which both inputs are used, add a series resistor to limit the input current. To ensure optimum dc and ac performance, balance the source impedance levels.

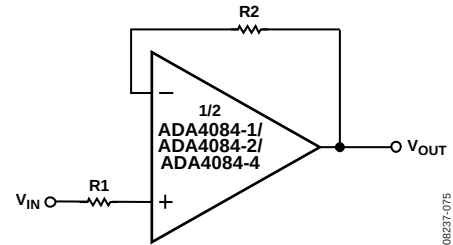


Figure 98. Resistance in Series with the Input Limits Overvoltage Currents to Safe Values

To protect the Q1/Q2 and Q3/Q4 pairs from large differential voltages that may result in Zener breakdown of the emitter-base junction, D100 and D101 are connected between the two inputs. This precludes operation as a comparator. For a more complete description, see the MT-035 Tutorial, *Op Amp Inputs, Outputs, Single-Supply, and Rail-to-Rail Issues*; the MT-083 Tutorial, *Comparators*; the MT-084 Tutorial, *Using Op Amps as Comparators*; and the AN-849 Application Note, *Using Op Amps as Comparators*.

OUTPUT PHASE REVERSAL

Some operational amplifiers designed for single-supply operation exhibit an output voltage phase reversal when their inputs are driven beyond their useful common-mode range. Typically, for single-supply bipolar op amps, the negative supply determines the lower limit of their common-mode range. With these devices, external clamping diodes, with the anode connected to ground and the cathode to the inputs, prevent input signal excursions from exceeding the negative supply of the device (that is, GND), preventing a condition that causes the output voltage to change phase. JFET input amplifiers can also exhibit phase reversal, and, if so, a series input resistor is usually required to prevent it.

The ADA4084-1/ADA4084-2/ADA4084-4 are free from reasonable input voltage range restrictions, provided that input voltages no greater than the supply voltages are applied (see Figure 32, Figure 61, and Figure 90).

Although device output does not change phase, large currents can flow through the input protection diodes. Therefore, apply the technique recommended in the Input Protection section to those applications where the likelihood of input voltages exceeding the supply voltages is high.

DESIGNING LOW NOISE CIRCUITS IN SINGLE-SUPPLY APPLICATIONS

In single-supply applications, devices like the [ADA4084-1/ADA4084-2/ADA4084-4](#) extend the dynamic range of the application through the use of rail-to-rail operation. Referring to the op amp noise model circuit configuration illustrated in Figure 99, the expression for the total equivalent input noise voltage of an amplifier for a source resistance level, R_s , is given by

$$e_{nT} = \sqrt{2[(e_{nR})^2 + (i_{nOA} \times R_s)^2] + (e_{nOA})^2}, \text{ units in } \frac{V}{\sqrt{\text{Hz}}}$$

where:

$(e_{nR})^2$ is the source resistance thermal noise voltage power ($4kTR$).
 k is the Boltzmann's constant, 1.38×10^{-23} J/K.

T is the ambient temperature in Kelvin of the circuit, $273.15 + T_A$ (°C).

$(i_{nOA})^2$ is the op amp equivalent input noise current spectral power (1 Hz bandwidth).

$R_s = 2R$, the effective, or equivalent, circuit source resistance.

$(e_{nOA})^2$ is the op amp equivalent input noise voltage spectral power (1 Hz bandwidth).

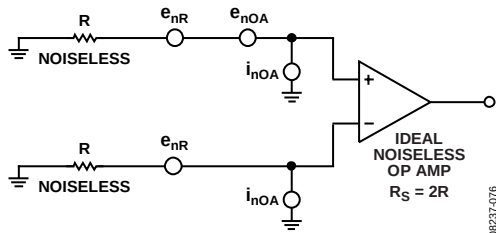


Figure 99. Op Amp Noise Circuit Model Used to Determine Total Circuit Equivalent Input Noise Voltage and Noise Figure

As a design aid, Figure 100 shows the equivalent thermal noise of the [ADA4084-1/ADA4084-2/ADA4084-4](#) vs. the total source resistance. Note that for source resistance less than 1 kΩ, the equivalent input noise voltage of the [ADA4084-1/ADA4084-2/ADA4084-4](#) is dominant.

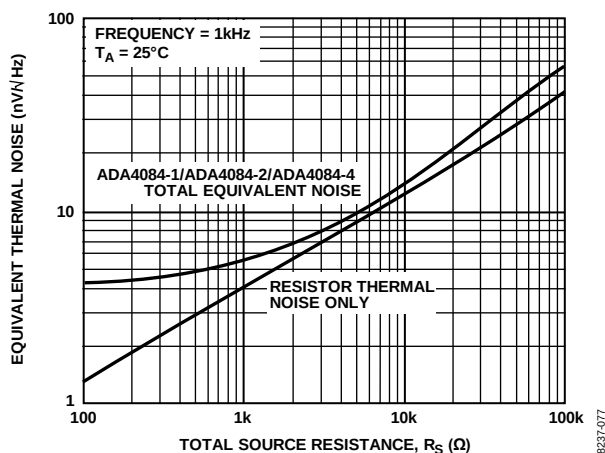


Figure 100. Equivalent Thermal Noise vs. Total Source Resistance

Because circuit SNR is the critical parameter in the final analysis, the noise behavior of a circuit is sometimes expressed in terms of its noise figure (NF). The noise figure is defined as the ratio of the signal-to-noise output of a circuit to its signal-to-noise input.

Noise figure is generally used for RF and microwave circuit analysis in a 50 Ω system. This is not very useful for op amp circuits where the input and output impedances can vary greatly. For a more complete description of noise figure, see the [MT-052 Tutorial](#), *Op Amp Noise Figure: Don't be Misled*.

Signal levels in the application invariably increase to maximize circuit SNR, which is not an option in low voltage, single-supply applications.

Therefore, to achieve optimum circuit SNR in single-supply applications, choose an operational amplifier with the lowest equivalent input noise voltage, along with source resistance levels that are consistent with maintaining low total circuit noise.

COMPARATOR OPERATION

Although op amps are quite different from comparators, occasionally an unused section of a dual or a quad op amp can be used as a comparator; however, this is not recommended for any rail-to-rail output op amps. For rail-to-rail output op amps, the output stage is generally a ratioed current mirror with bipolar or MOSFET transistors. With the device operating open loop, the second stage increases the current drive to the ratioed mirror to close the loop. However, the loop cannot close, which results in an increase in supply current. With the op amp configured as a comparator, the supply current can be significantly higher (see Figure 101). Configure an unused section as a voltage follower with the noninverting input connected to a voltage within the input voltage range. The [ADA4084-1/ADA4084-2/ADA4084-4](#) have unique second stage and output stage designs that greatly reduce the excess supply current when the op amp is operating open loop.

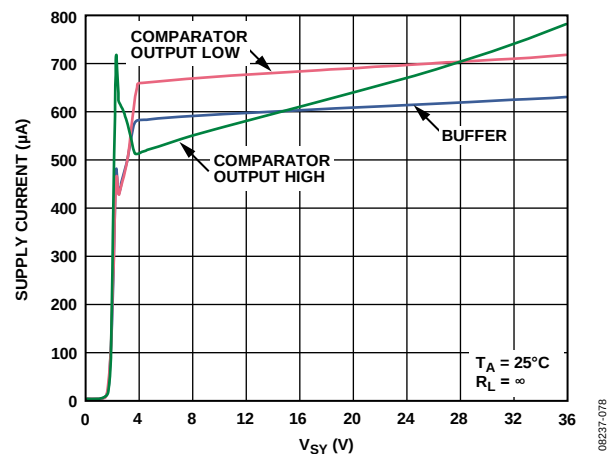
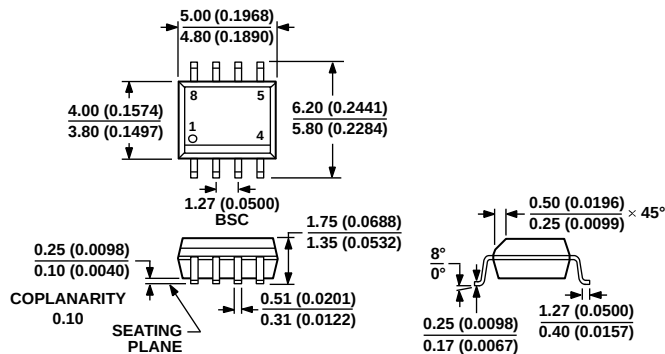


Figure 101. Supply Current vs. Supply Voltage (V_{SV})

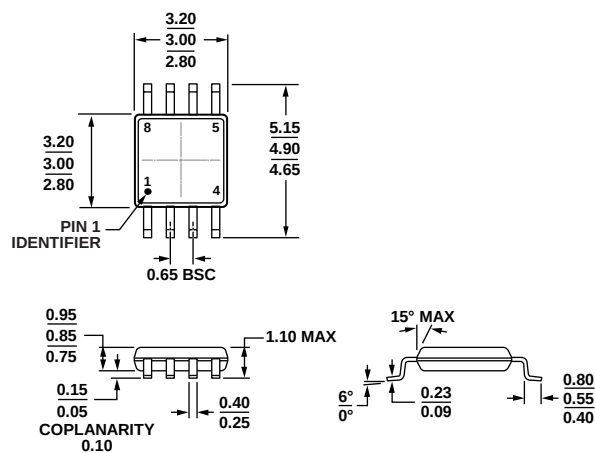
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-012-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 102. 8-Lead Standard Small Outline Package [SOIC_N]
Narrow Body
(R-8)

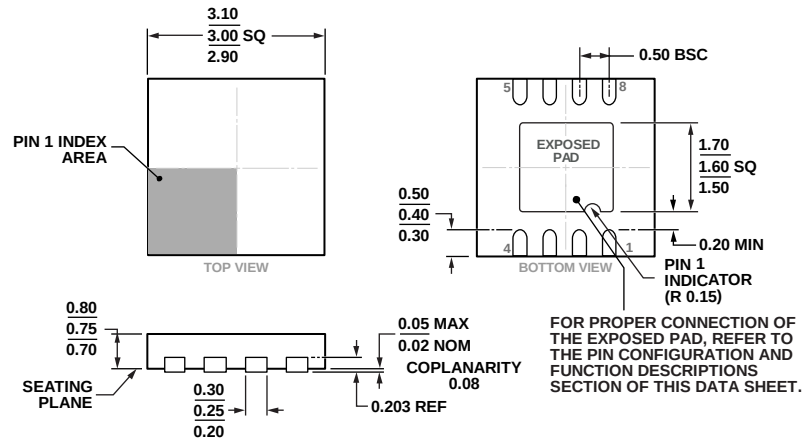
Dimensions shown in millimeters and (inches)



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 103. 8-Lead Mini Small Outline Package [MSOP]
(RM-8)

Dimensions shown in millimeters

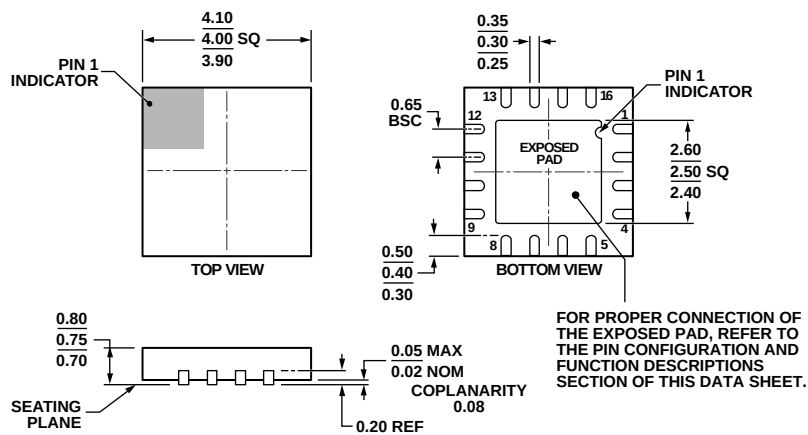


COMPLIANT TO JEDEC STANDARDS MO-229-WEED

Figure 104. 8-Lead Lead Frame Chip Scale Package [LFCSP_WD]
3 mm × 3 mm Body, Very Very Thin, Dual Lead
(CP-8-12)

Dimensions shown in millimeters

02-05-2013-B

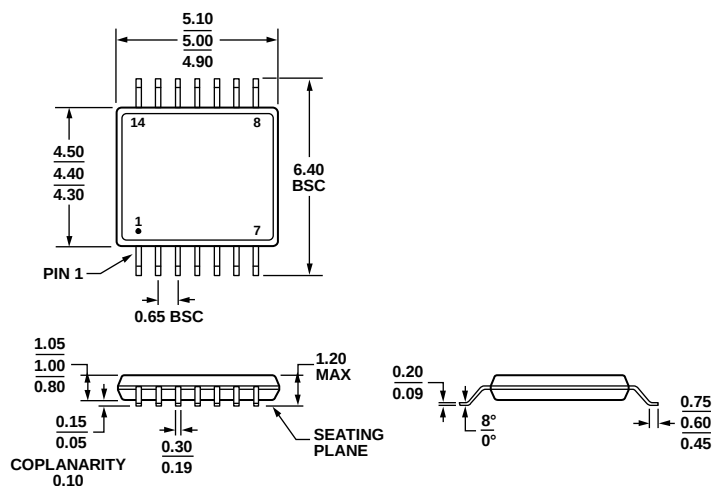


COMPLIANT TO JEDEC STANDARDS MO-220-WGGC.

Figure 105. 16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]
4 mm × 4 mm Body, Very Very Thin Quad
(CP-16-26)

Dimensions shown in millimeters

042709-A



COMPLIANT TO JEDEC STANDARDS MO-153-AB-1

Figure 106. 14-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-14)

Dimensions shown in millimeters

061908-A

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option	Branding
ADA4084-1ARZ	−40°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8	
ADA4084-1ARZ-R7	−40°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8	
ADA4084-1ARZ-RL	−40°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8	
ADA4084-2ARMZ	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A2Q
ADA4084-2ARMZ-R7	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A2Q
ADA4084-2ARMZ-RL	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	A2Q
ADA4084-2ARZ	−40°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8	
ADA4084-2ARZ-R7	−40°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8	
ADA4084-2ARZ-RL	−40°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8	
ADA4084-2ACPZ-R7	−40°C to +125°C	8-Lead Lead Frame Chip Scale Package [LFCSP_WD]	CP-8-12	A2Q
ADA4084-2ACPZ-RL	−40°C to +125°C	8-Lead Lead Frame Chip Scale Package [LFCSP_WD]	CP-8-12	A2Q
ADA4084-4ACPZ-R7	−40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-16-26	
ADA4084-4ACPZ-RL	−40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_WQ]	CP-16-26	
ADA4084-4ARUZ	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14	
ADA4084-4ARUZ-RL	−40°C to +125°C	14-Lead Thin Shrink Small Outline Package [TSSOP]	RU-14	

¹ Z = RoHS Compliant Part.